



## MONITOR MICROCONTROLLER

### GENERAL DESCRIPTION

The W78E354 is a stand-alone high-performance microcontroller ASIC specially designed for use in monitor control applications. Using the Winbond 0.8 $\mu$  DPDM process, the W78E354 integrates an embedded 8031 microcontroller core, 16K bytes of Flash cell, 512 bytes of RAM and a number of dedicated hardware functions. These hardware functions include a 6-bit A/D converter, two/fourteen 12/8-bit PWM static DACs, one/three 12/8-bit PWM dynamic DACs, a sync processor, one DDC port, a watchdog timer and other custom glue logic. Additional special function registers are incorporated to control the on-chip peripheral hardware.

The chip is used to control the interface signals of other devices in the monitor and to process the video sync signals. Because of high integration and the incorporation of Flash cell for program memory, the device offers the user the competitive advantages of low cost and reduced development time.

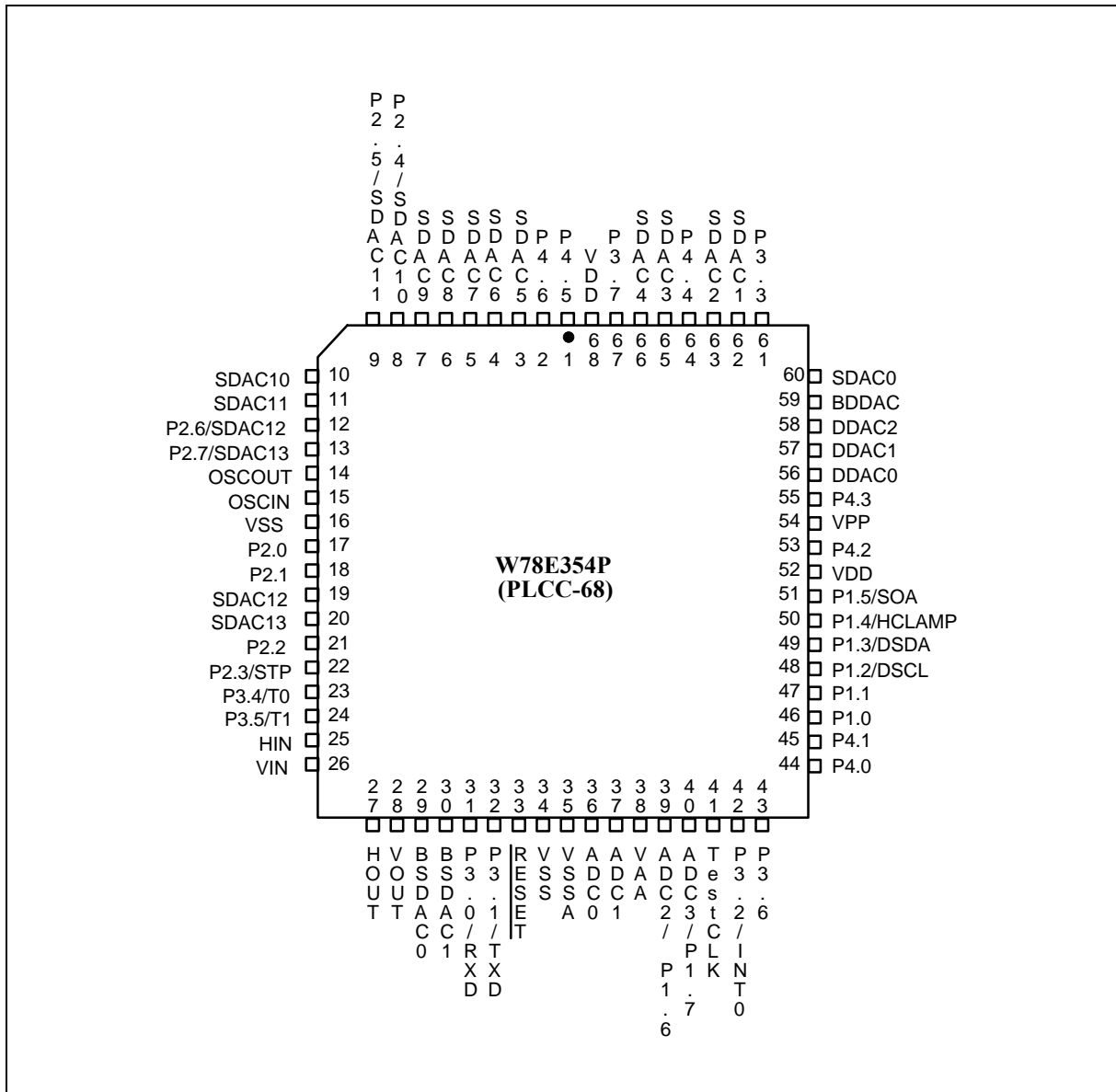
### FEATURES

- 80C31 MCU core included
- 16K bytes Flash OTP memory for program storage
- Total 512 bytes of on-chip data RAM:  
256 bytes accessed as in the 80C32, 256 bytes accessed as external data memory via "MOVX @Ri".
- One SPI/RS232 port (a serial port of 8051 standard)
- One external interrupt input
- Two timers/counters
- PWM DACs:
  - Two 12-bit PWM/BRM Static DACs
  - Fourteen 8-bit PWM Static DACs
  - One 12-bit PWM/BRM Dynamic DAC
  - Three 8-bit PWM Dynamic DACs
- One 6-bit ADC with 4 multiplexed analog inputs
- Sync Processor:
  - Horizontal & Vertical Polarity Detector
  - Sync Separator for composite sync
  - Horizontal & Vertical Frequency Counter
  - Programmable dummy frequency generator
  - Programmable H-clamp pulse output
  - SOA output (hardware H frequency change detection)
- One DDC port (master/slave mode I<sup>2</sup>C with two slave address reg., support DC1/DDC2B/DDC2B+)
- One 8-bit Auto-reload timer for software time base



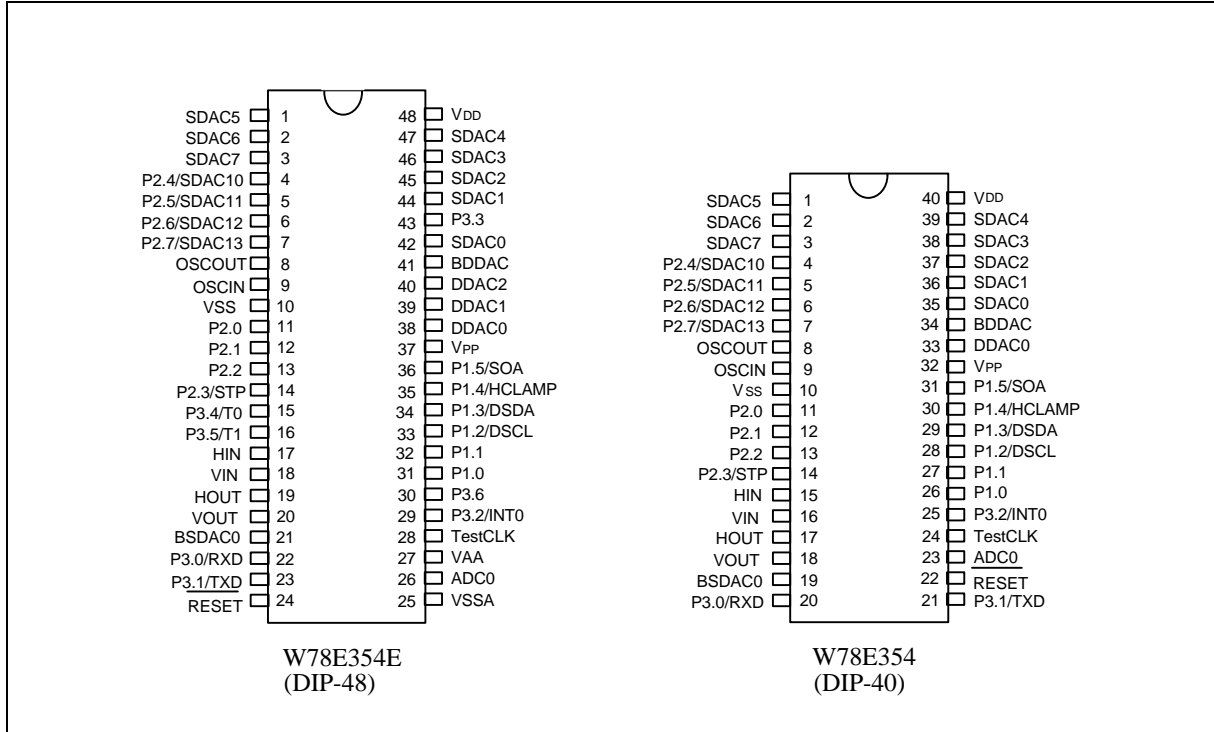
- Watchdog Timer
- Two 15 mA output pins for driving LEDs
- Power down reset
- Clock: DC to 20 MHz
- Packaged in 68-pin PLCC, 48-pin DIP and 40-pin DIP

## PIN CONFIGURATIONS





Pin Cnfigurations, continued



## PIN DESCRIPTION

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
60	57	42	35	SDAC0	I/O	A0	8-bit PWM static DAC output.
62	59	44	36	SDAC1		A1	Sink/Source current 4 mA/-4 mA.
63	60	45	37	SDAC2		A2	With <b><i>slew rate control</i></b> and <b><i>output delay</i></b> :
65	61	46	38	SDAC3		A3	1. Delay about 5 nS:
66	62	47	39	SDAC4		A4	SDAC2, 5, 8, 11.
3	1	1	1	SDAC5		A5	2. Delay about 10 nS:
4	2	2	2	SDAC6		A6	SDAC0, 3, 6, 9, 12.
5	3	3	3	SDAC7		A7	3. Without delay: the others.
6	4	-	-	SDAC8	O/P	-	* In the Flash/RAM-test mode
7	5	-	-	SDAC9		-	(when the chip is in reset state):
10	8	-	-	SDAC10		-	SDAC0-7: A0-A7 inputs.
11	9	-	-	SDAC11		-	* In the functional test mode
19	17	-	-	SDAC12		-	(CPU executes out of ext. program memory):
20	18	-	-	SDAC13		-	SDAC0-7: A0-A7 outputs.



## Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
29	27	21	19	BSDAC0	I/O	A8	12-bit PWM/BRM static DAC output. Sink/Source current 8 mA/-8 mA. With <b><u>slew rate control</u></b> and <b><u>output delay</u></b> : 1. Delay about 5ns: BSDAC1 2. Without delay: BSDAC0. ----- * In the Flash/RAM-test mode (when the chip is in reset state): BSDAC0: A8 input. * In the functional test mode (CPU executes out of ext. program memory): BSDAC0: A8 output.
30	28	-	-	BSDAC1	O/P	-	
56	53	38	33	DDAC0	I/O	A9	8-bit PWM dynamic DAC output. Sink/Source current 8 mA/-8 mA. With <b><u>slew rate control</u></b> and <b><u>output delay</u></b> : 1. Delay about 5 nS: DDAC1. 2. Delay about 10 nS: DDAC2. 3. Without delay: DDAC0. ----- * In the Flash/RAM-test mode (when the chip is in reset state): DDAC0: A9 input. * In the functional test mode (CPU executes out of ext. program memory): DDAC0: A9 output.
57	54	39	-	DDAC1	O/P	-	
58	55	40	-	DDAC2		-	
59	56	41	34	BDDAC	I/O	A10	12-bit PWM/BRM dynamic DAC output. Sink/Source current 8mA/-8mA. With <b><u>slew rate control</u></b> . ----- * In the Flash/RAM-test mode (when the chip is in reset state): BDDAC: A10 input. * In the functional test mode (CPU executes out of ext. program memory): BDDAC: A10 output.



Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
36	34	26	23	ADC0	I/P	-	Analog signal input channel to ADC.
37	35	-	-	ADC1		-	Alternate function:
39	37	-	-	ADC2 (P1.6)		-	ADC2: P1.6 input (input only).
40	38	-	-	ADC3 (P1.7)		-	ADC3: P1.7 input (input only).
46	44	31	26	P1.0	I/O	A13	General purpose I/O.
47	45	32	27	P1.1		A14	Open-drain, Sink current 2mA. Schmitt trigger I/P. No PMOS ESD cell. <b>V<sub>IH</sub> = 3.0V (min), V<sub>IL</sub> = 1.5V (max)</b> ----- * In the Flash/RAM-test mode (when the chip is in reset state): P1.0 and P1.1: A13 and A14 inputs. * In the functional test mode (CPU executes out of ext. program memory): P1.0 and P1.1: <i>do not output A13 and A14, but function in their normal operational state.</i>
48	46	33	28	P1.2 (DSCL)	I/O	A13CTRL	General purpose I/O.
49	47	34	29	P1.3 (DSDA)		A14CTRL	Open-drain, Sink current 6mA. Schmitt trigger I/P. No PMOS ESD cell. <b>V<sub>IH</sub> = 3.0V (min), V<sub>IL</sub> = 1.5V (max)</b> Alternate function: P1.2: DDC port serial clock DSCL. P1.3: DDC port serial data DSDA. ----- * In the Flash/RAM-test mode (when the chip is in reset state): P1.2: A13CTRL input. P1.3: A14CTRL input.



## Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
50	48	35	30	P1.4 (HCLAMP)	I/O	A9CTRL	<p>General purpose I/O. Sink/Source current 4 mA/-100 <math>\mu</math>A.</p> <p><b>Alternate function:</b></p> <p>P1.4: HCLAMP (H-clamp pulse) output. <b>While outputting special function, P1.4's Sink/Source current is 4 mA/-4 mA.</b></p> <p>-----</p> <p>* In the Flash/RAM-test mode (when the chip is in reset state): P1.4: A9CTRL input.</p>
51	49	36	31	P1.5 (SOA)	I/O	A11	<p>General purpose O/P. Sink/Source current 4 mA/-4 mA.</p> <p><b>Alternate function:</b></p> <p>P1.5: SOA (Safe Operation Area) output.</p> <p>-----</p> <p>* In the Flash/RAM-test mode (when the chip is in reset state): P1.5: A11 input.</p> <p>* In the functional test mode (CPU executes out of ext. program memory): P1.5: <i>doesn't output A11, but functions as its normal operation.</i></p>
17 18	15 16	11 12	11 12	P2.0 P2.1	I/O	D0 D1	<p>General purpose I/O. Sink/Source current 15mA/-100<math>\mu</math>A. With <b><i>slew rate control</i></b> .</p> <p>-----</p> <p>* In the Flash/RAM-test mode (when the chip is in reset state): P2.0–P2.1: D0–D1 data inputs/outputs.</p> <p>* In the functional test mode (CPU executes out of ext. program memory): P2.0–P2.1: D0–D1 program inputs.</p>



Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION		
68P	64P	48P	40P						
21	19	13	13	P2.2 P2.3 (STP) P2.4 (SDAC10) P2.5 (SDAC11) P2.6 (SDAC12) P2.7 (SDAC13)	I/O	D2	General purpose I/O.		
22	20	14	14			D3	Sink/Source current 4 mA/-100 μA.		
8	6	4	4			D4	Alternate function:		
9	7	5	5			D5	P2.3: STP (Self-Test Pattern) output.		
12	10	6	6			D6	P2.4–P2.7: SDAC10–13 outputs.		
13	11	7	7			D7	<b>While outputting special function, P2.3–P2.7's Sink/Source current is 4mA/4mA.</b>		
-----									
* In the Flash/RAM-test mode (when the chip is in reset state): P2.2–P2.7: D2–D7 data inputs/outputs.									
* In the functional test mode (CPU executes out of ext. program memory): P2.2–P2.7: D2–D7 program inputs.									
31	29	22	20			P3.0 (RXD) P3.1 (TXD) P3.2 (INT0) P3.3 P3.4 (T0) P3.5 (T1) P3.6 P3.7	I/O	-	General purpose I/O.
32	30	23	21					-	Sink/Source current 2 mA/-100 μA.
42	40	29	25					A12 <b>(PSEN)</b>	Alternate function:
61	58	43	-					-	P3.0: 8051 serial input port.
23	21	15	-	-	P3.1: 8051 serial output port.				
24	22	16	-	-	P3.2: External interrupt input.				
43	41	30	-	-	P3.4 and P3.5: Timer/counter 0 and 1 external inputs.				
67	63	-	-	-	-----				
* In the Flash/RAM-test mode (when the chip is in reset state): P3.2: A12 input.									
* In the functional test mode (CPU executes out of ext. program memory): P3.2: <b>PSEN</b> output (the read strobe to external program memory) instead of A12.									



Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
44	42	-	-	P4.0	O/P	-	Output port (Latch output). Sink/Source current 2 mA/-2 mA.
45	43	-	-	P4.1		-	
53	51	-	-	P4.2		-	
55	-	-	-	P4.3		-	
64	-	-	-	P4.4		-	
1	-	-	-	P4.5		-	
2	-	-	-	P4.6		-	
25	23	17	15	HIN	I/P	$\overline{\text{OE}}$	HIN: Hsync/Composite sync input. VIN: Vsync input. Schmitt trigger I/P. With Internal high value pull-down (about 200 K $\Omega$ ). No PMOS ESD diode. ----- * In the Flash/RAM-test mode (when the chip is in reset state): HIN: $\overline{\text{OE}}$ input. VIN: $\overline{\text{CE}}$ input.
26	24	18	16	VIN		$\overline{\text{CE}}$	
27	25	19	17	HOUT	I/O	$\overline{\text{OCTRL}}$	
28	26	20	18	VOUT		$\overline{\text{PROG}}$	
HOUT: Hsync output. VOUT: Vsync output with internal weak pull-up (above 200 K $\Omega$ ). Sink/Source current 4 mA/-4 mA. ----- * In the Flash/RAM-test mode (when the chip is in reset state): HOUT: $\overline{\text{OCTRL}}$ input. VOUT: $\overline{\text{PROG}}$ input.							
33	31	24	22	$\overline{\text{RESET}}$	I/P	-	Reset the controller (active low). Schmitt trigger I/P. With internal pull-up (about 30 K $\Omega$ ).
41	39	28	24	TestCLK	I/P	$\overline{\text{EA}}$	Clock input while in internal (glue logic's) function test. With internal pull-up (about 30 K $\Omega$ ). ----- * If the EA (TestCLK) pin is pulled low when the chip is being reset, and remains low for at least 24 clock periods after the reset, the CPU will execute from the external program memory regardless of the PC value. i.e., the CPU is forced to enter the <i>functional test mode</i> .

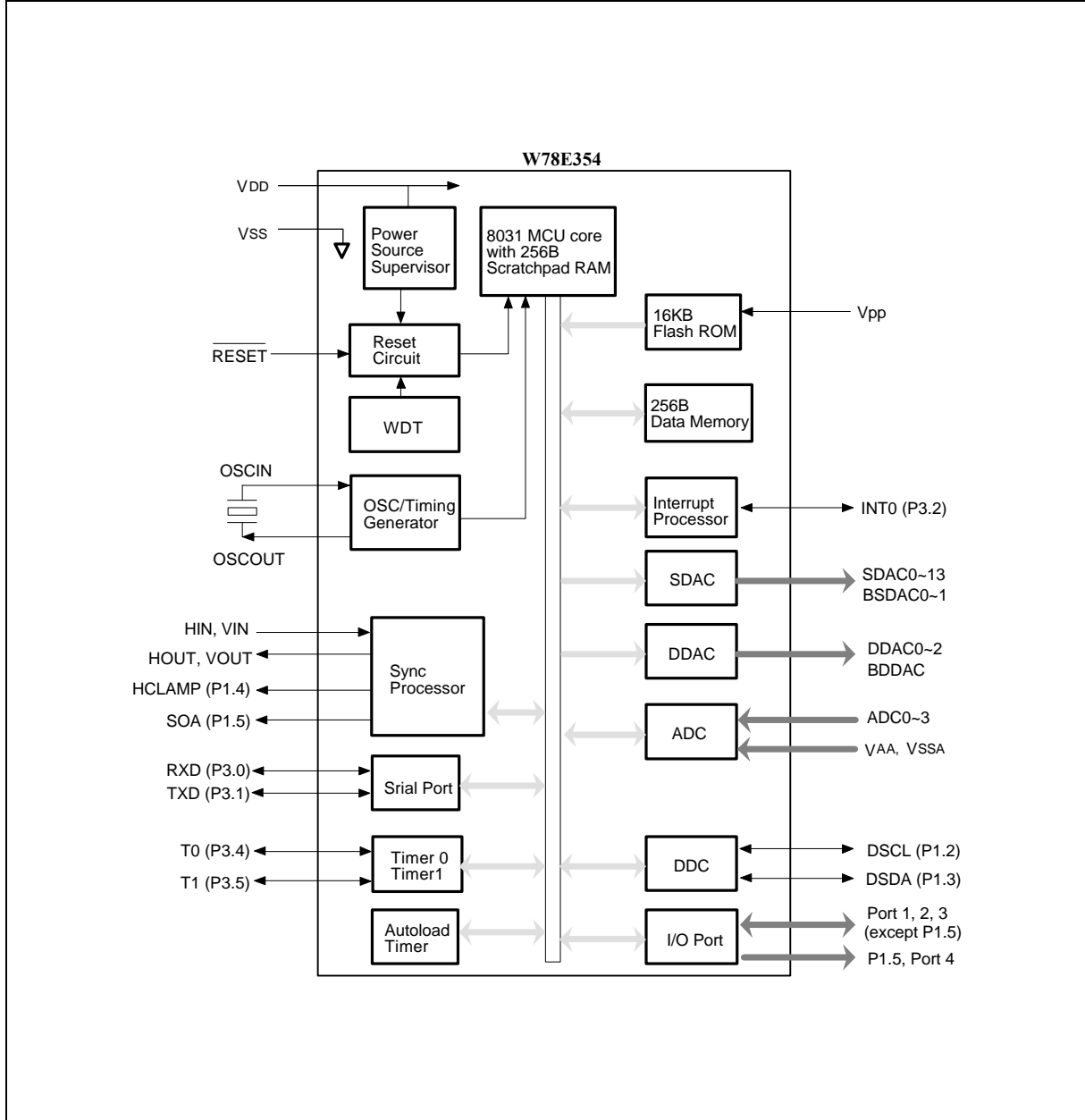




Pin Description, continued

PIN NO.				PIN NAME	I/O TYPE	TEST NAME	FUNCTIONAL DESCRIPTION
68P	64P	48P	40P				
14	12	8	8	OSC <sub>OUT</sub>	O/P	-	Output from the inverting oscillator amplifier.
15	13	9	9	OSC <sub>IN</sub>	I/P	-	Input to the inverting oscillator amplifier. Freq.: 16 MHz to 24 MHz.
54	52	37	32	V <sub>PP</sub>	-	V <sub>PP</sub>	In the Test/Flash mode, this pin is the power supply input for the Flash cell.
68	64	48	40	V <sub>DD</sub>	-	-	Positive digital power supply, +5V.
16	14	10	10	V <sub>SS</sub>	-	-	Digital ground.
52	50	-	-	V <sub>DD</sub>	-	-	Positive digital power supply, +5V. Internally connected to the other power source.
34	32	-	-	V <sub>SS</sub>	-	-	Digital ground. Internally connected to the other power source.
38	36	27	-	V <sub>AA</sub>	-	-	Positive analog power supply, +5V.
35	33	25	-	V <sub>SSA</sub>	-	-	Analog ground.

## BLOCK DIAGRAM





## FUNCTIONAL DESCRIPTION

### A. 80C31 Core

The W78E354's 80C31 (CMOS MCU) core architecture consists of a CPU surrounded by various Special Function Registers or SFRs. Some of these SFRs are standard 80C31 registers while others are new additions, cf. Table 1. The device includes three general purpose I/O ports (P1, P2 and P3), one output-only port (P4), 256 bytes of scratchpad RAM, two timer/counters (Timer0 and Timer1) and one 8051 standard serial port. The processor supports 109 different instructions (without "MOVX A,@DPTR" and "MOVX @DPTR,A") all of which are compatible with those of the MCS-51 family.

One distinguishing feature of the device architecture is the SFR address space into which all the registers, peripherals and scratchpad RAM are mapped. Many of the instructions operate on an SFR address rather than a specific register, greatly increasing the power of the instruction set.

The core controller has been designed around a state machine rather than utilizing a microcode approach, a design methodology which offers several advantages. The first of these is that faster circuits can be produced due to the fact that flip-flops are inherently faster than ROMs. Secondly, a ROM-free approach allows the design to be directly utilized in ASIC gate array implementations, an important factor for cost reductions. Finally, an entire digital logic approach provides better supply noise immunity in most applications.

**Table 1. W78E354's Special Function Registers (SFRs)**

F8									FF
F0	+ B								F7
E8									EF
E0	+ ACC								E7
D8	+ S1CON	S1STA	S1DAT	S1ADR					DF
D0	+ PSW								D7
C8	+ CONTREG4								CF
C0									C7
B8	+ IP	SBRM0	SBRM1	PORT4	SOAREG	SOACLK			BF
B0	+ P3	ADC	INTVECT	STATUS	HFCOUNTL	HFCOUNTH	VFCOUNTL	VFCOUNTH	B7
A8	+ IE	SDAC7	SDAC8	SDAC9	SDAC10	SDAC11	SDAC12	SDAC13	AF
A0	+ P2	SDAC0	SDAC1	SDAC2	SDAC3	SDAC4	SDAC5	SDAC6	A7
98	+ SCON	SBUF	BSDAC0	BSDAC1	WDTCLR	DDAC0	DDAC1	DDAC2	9F
90	+ P1	AUTOLOAD	DHREG	DVREG	DDC1	INTMSK	BDDAC	DBRM	97
88	+ TCON	TMOD	TL0	TL1	TH0	TH1	PARAL	PARAH	8F
80	+ CONTREG1	SP	DPL	DPH	CONTREG5	CONTREG2	CONTREG3	PCON	87

Notes:

1. The SFRs with a "+" are both byte- and bit-addressable.
2. The registers in the shaded region are new additions to the 80C31 SFRs.

#### A.1 Address Space (cf. Figure 1)

The W78E354 CPU operates out of three separate address spaces:



1. The first of these is the internal program space (internal Flash memory) with 16K byte size (0000H–3FFFH). The program space can be accessed by both opcode fetches and the "MOVC" instructions.
2. The second is referred to as the data memory space and has a size of 256 bytes (0000H–00FFH). The data memory is integrated within the chip rather than being outside as in the case of the standard 8031. The "inside" data memory space is accessed by the "MOVX @Ri" instruction.
3. The third address space has 256 locations while it is used by 384 bytes (256 bytes of RAM and 128 bytes of SFRs).
  - The lower 128 locations of this address space (00H–7FH) are for the lower 128 bytes of scratchpad RAM. Any of these 128 bytes may be used by a programmer but some of them have special uses. The lowest 32 bytes are organized to four 8-byte register banks. The bank select bits (RS0 and RS1 in the PSW register) selects one of these four banks which is to be used currently as an operand in the instruction set. Registers 0 to 7 in the bank are referenced by the register direct opcodes. Registers 0 and 1 may also contain an address that is referenced by the register indirect opcodes.
  - The higher 128 locations of this address space (80H–FFH) are shared by the higher 128 bytes of scratchpad RAM and the Special Function Registers (SFRs). The SFRs are accessed only by "direct" addressing while the higher 128 bytes of scratchpad RAM are accessed only by "indirect" addressing. The higher 128 bytes of scratchpad data RAM are also available for stack space.

Address spaces 20H to 2FH are bit-addressable and can be used by the Boolean Variable Manipulation instructions. For example, bit 0 of address 20H has a Boolean address 00H, and bit 7 of address 2FH has a Boolean address 7FH. The higher Boolean addresses (80H–FFH) are mapped into the SFR address space. To determine a Boolean address in some bit-addressable SFR, the higher 5 bits of the SFR's address can be combined with the 3 lower bits that specify the desired bit in the SFR.

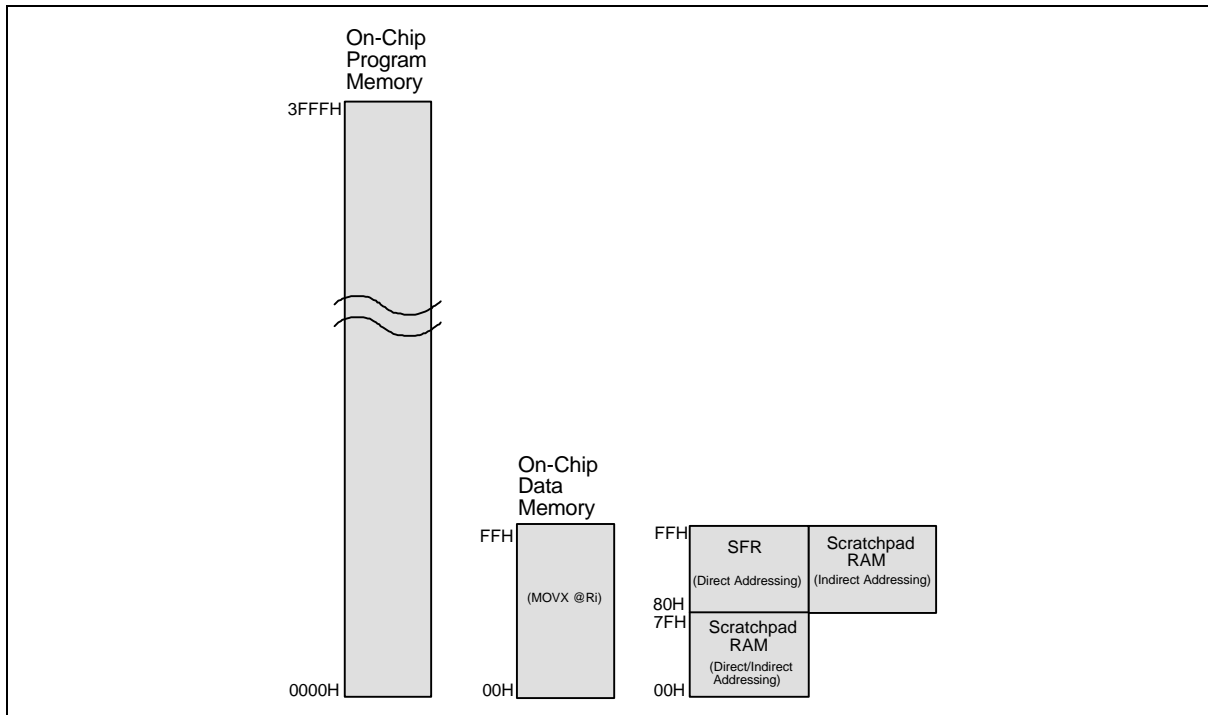


Figure1. Address Space



## A.2 The Modified 80C31 SFRs

### 1. Timer/Counter Control Register: TCON

BIT	NAME	FUNCTION
TCON.7	TF1	Timer 1 overflow flag. Set by hardware on timer/counter overflow. Cleared by hardware when the processor vectors to the interrupt routine.
TCON.6	TR1	Timer 1 run control bit. Set/cleared by software to turn the timer/counter on or off.
TCON.5	TF0	Timer 0 overflow flag. Set by hardware on timer/counter overflow. Cleared by hardware when the processor vectors to the interrupt routine.
TCON.4	TR0	Timer 0 run control bit. Set/cleared by software to turn the timer/counter on or off.
TCON.3	-	(Reserved, not used by users.)
TCON.2	-	(Reserved)
TCON.1	IE0	Interrupt 0 edge flag. Set by hardware when an external interrupt edge is detected. Cleared when the interrupt is processed.
TCON.0	IT0	Interrupt 0 type control bit. Set/cleared by software to specify falling edge/low level triggered external interrupt.

### 2. Power Control Register: PCON

BIT	NAME	FUNCTION
7	SMOD	Double baud rate bit.
6	-	(Reserved)
5	-	(Reserved, not used by users.)
4	-	(Reserved for testing, not used by users. Normally 0. If set, P2.4–P2.7 will output SDAC8-11 after reset (not power-on reset).)
3	GF1	General-purpose flag bit.
2	GF0	General-purpose flag bit.
1	PD	Power-down mode bit.
0	IDL	Idle mode bit.



## 3. Interrupt Enable Register: IE

BIT	NAME	FUNCTION
IE.7	EA	If EA = 0, no interrupt will be acknowledged (disable all interrupts). If EA = 1, each interrupt source is individually enabled or disabled by setting or clearing its enable bit.
IE.6	-	(Reserved)
IE.5	*1	Set/clear to enable/disable the DDC port's I <sup>2</sup> C interrupt.
IE.4	ES	Set/clear to enable/disable the serial port 0 interrupt.
IE.3	ET1	Set/clear to enable/disable the Timer 1 overflow interrupt.
IE.2	*1	Set/clear to enable/disable the *2 interrupt.
IE.1	ET0	Set/clear to enable/disable the Timer 0 overflow interrupt.
IE.0	EX0	Set/clear to enable/disable the external interrupt 0.

## Notes:

\*1: No name for ASSEMBLER, must be used via "IE.x".

\*2 = (DSCLINT + ADCINT + TIMEOUT + SOAINT + VEVENT + PARAINIT + DDC1INT).

## 4. Interrupt Priority Register: IP

BIT	NAME	FUNCTION
IP.7	-	(Reserved)
IP.6	-	(Reserved)
IP.5	*1	Define the DDC port's I <sup>2</sup> C interrupt priority level. If IP.5 = 1, the priority level is higher.
IP.4	PS	Define the serial port interrupt priority level. If PS = 1, the priority level is higher.
IP.3	PT1	Define the Timer 1 interrupt priority level. If PT1 = 1, the priority level is higher.
IP.2	*1	Define the *2 priority level. If IP.2 = 1, the priority level is higher.
IP.1	PT0	Define the Timer 0 interrupt priority level. If PT0 = 1, the priority level is higher.
IP.0	PX0	Define the external interrupt 0 priority level. If PX0 = 1, the priority level is higher.

## Notes:

\*1: No name for ASSEMBLER, must be used via "IP.x".

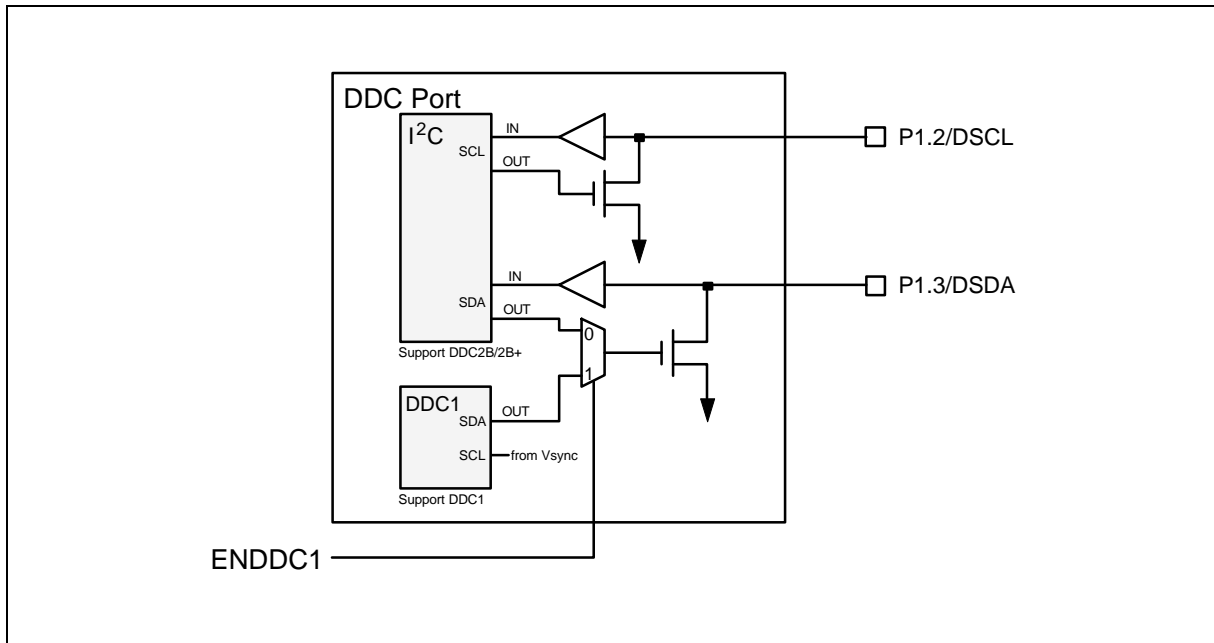
\*2 = (DSCLINT + ADCINT + TIMEOUT + SOAINT + VEVENT + PARAINIT + DDC1INT).





\* **CONTREG1**: Control register1, bit-addressable.

BIT	NAME	FUNCTION	NOTE
0	ADCS0	ADC channel Select bit 0	See Section E.10.
1	ADCS1	ADC channel Select bit 1	See Section E.10.
2	ENDDC1	Enable DDC1	See below.
3	HCES	H-Clamp Edge Select	See Section E.12.f.
4	HCWS0	H-Clamp Width Select bit 0	See Section E.12.f.
5	HCWS1	H-Clamp Width Select bit 1	See Section E.12.f.
6	DUMMYEN	Dummy signal Enable	See Section E.12. 'Sync Processor Block Diagram' & E.12.e.
7	ADCSTRT	Start ADC conversion 0: Stop, 1: Start	See Section E.10.

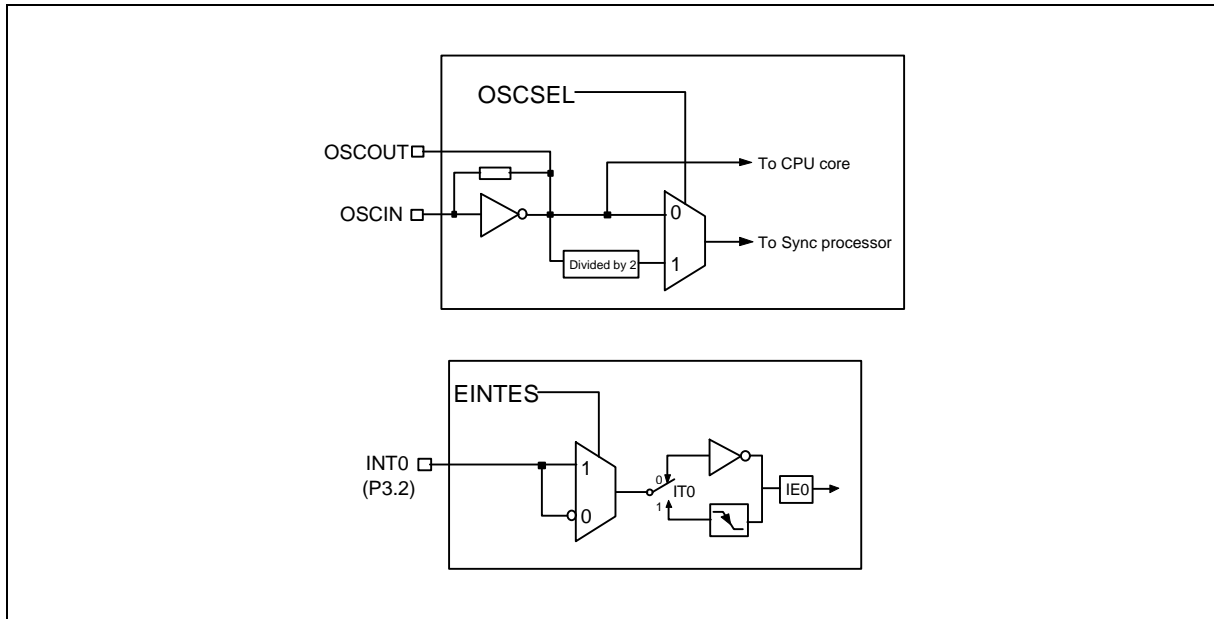






\* **CONTREG2:** Control register2.

BIT	NAME	FUNCTION	NOTE
0	ENVS	ENable Vsync Separator	See Section E.12. 'Sync Processor Block Diagram' & E.12.e.
1	HSPS	HSync Polarity Select 0: Positive, 1: Negative	See Section E.12. 'Sync Processor Block Diagram'.
2	VSPS	VSynC Polarity Select 0: Positive, 1: Negative	See Section E.12. 'Sync Processor Block Diagram'.
3	OSCSEL	OSC or OSC/2 SElect	See below.
4	EINTES	External INT Edge Select 0: High-level/rising-edge triggered 1: Low-level/falling-edge triggered	See below.
5	ENM0	ENable SDAC0 Moire cancel function 0: Disable, 1:Enable	
6	ENM1	ENable SDAC1 Moire cancel function 0: Disable, 1:Enable	
7	VDISHC	Vsync DISable H-Clamp pulse 0: Enable, 1:Disable	See Section E.12. 'Sync Processor Block Diagram'.





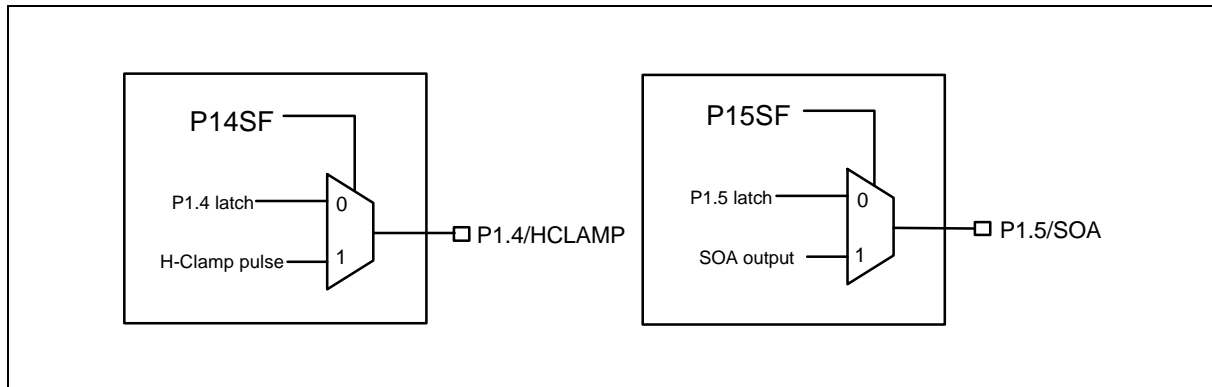
\***CONTREG3:** Control register3.

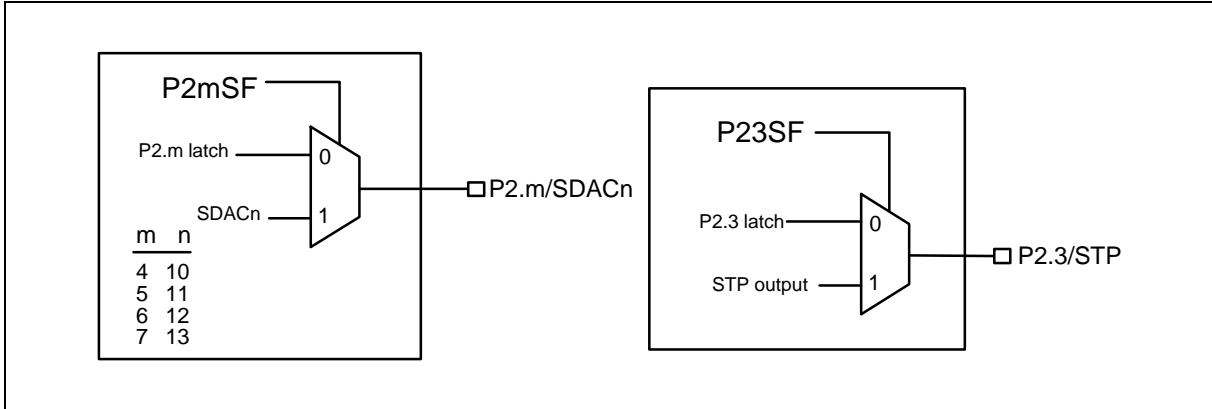
BIT	NAME	FUNCTION	NOTE
0	P4SF	Port 4 Special Function	
1	TSTMOD1	Function test mode1	
2	TSTMOD2	Function test mode2	
3	TSTMOD3	Function test mode3	
4	TVSEP	Test VSEP signal	
5	-	(Reserved for internal use.)	
6	-	(Reserved for internal use.)	
7	-	(Reserved for internal use.)	

\***CONTREG4:** Control register4, bit-addressable.

BIT	NAME	FUNCTION	NOTE
0	P24SF	Port 2.4 Special Function* (SDAC10)	See below.
1	P25SF	Port 2.5 Special Function* (SDAC11)	See below.
2	P26SF	Port 2.6 Special Function* (SDAC12)	See below.
3	P27SF	Port 2.7 Special Function* (SDAC13)	See below.
4	P14SF	Port 1.4 Special Function*	See below.
5	P15SF	Port 1.5 Special Function*	See below.
6	P23SF	Port 2.3 Special Function*	See below.
7	INVSTP	Invert Self-Test Pattern	

\*Note:In addition to setting PxySF, the port latch Pxy must have been cleared previously to enable the Pxy output special functions.





\***CONTREG5:** Control register5.

BIT	NAME	FUNCTION	NOTE
0			
1			
2			
3			
4			
5	HDSEL	HCLAMP Source SElect	
6	DPARAINT	Enable parabola with dummy Sync.	
7			

\* **STATUS:** Status register.

BIT	NAME	FUNCTION
0	HP	Hsync polarity. 0: Positive, 1: Negative.
1	VP	Vsync polarity. 0: Positive, 1: Negative.
2	NOH	Set by hardware if no Hsync.
3	NOV	Set by hardware if no Vsync.



\* **INTMSK**: Interrupt mask register.

BIT	NAME	FUNCTION
0	DSCLINTmsk	Set/clear to enable/disable DSCLINT interrupt.
1	ADCINTmsk	Set/clear to enable/disable ADCINT interrupt.
2	TIMEOUTmsk	Set/clear to enable/disable TIMEOUT interrupt.
3	SOAINTmsk	Set/clear to enable/disable SOAINT interrupt.
4	VEVENTmsk	Set/clear to enable/disable VEVENT interrupt.
5	PARAINTmsk	Set/clear to enable/disable PARAINT interrupt.
6	DDC1INTmsk	Set/clear to enable/disable DDC1INT interrupt.
7		

Note: A '1' in any bit of the INTMSK register enables the corresponding interrupt flag in INTVECT to be set by hardware when the interrupt source generates an interrupt.

\* **INTVECT**: Interrupt vector register.

BIT	NAME	FUNCTION	NOTE
0	DSCLINT	Set by hardware when DSCL is toggled from High to Low and kept Low for at least 12/Fosc sec.	See Section E.6.
1	ADCINT	Set by hardware when ADC conversion is completed.	See Section E.10.
2	TIMEOUT	Set by hardware when Autoload timer timeout.	See Section E.8.
3	SOAINT	Set by hardware when SOA is High.	See Section E.12.g.
4	VEVENT	Set by hardware when Vsync or Vertical frequency counter timeout.	
5	PARAINT	For parabola interrupt generator (set by hardware).	See Section E.9.
6	DDC1INT	For DDC1 of DDC port (set by hardware).	See Section E.6.
7			

Note: To clear the interrupt flag, write a '1' (not '0') to the corresponding bit in INTVECT register.

- \* **PARAL**: Parabola interrupt generator register, low byte.
- \* **PARAH**: Parabola interrupt generator register, high byte.
- \* **AUTOLOAD**: 8-bit Auto-reload timer register. (See Section H.)
- \* **DHREG**: Dummy Hsync frequency generator register. (See Section L.e.)
- \* **DVREG**: Dummy Vsync frequency generator register. (See Section L.e.)
- \* **DDC1**: DDC port's DDC1 data buffer.
- \* **DDAC0–DDAC2**: 8-bit PWM dynamic DAC register. (See Section K.)
- \* **BDDAC** (8 bits)+**DBRM** (4 bits): 12-bit PWM/BRM dynamic DAC register. (See Section K.)
- \* **SDAC0–SDAC13**: 8 bits, 8-bit PWM static DAC register. (See Section K.)
- \* **BSDAC0** (8 bits)+**SBRMO** (4 bits): 12-bit PWM/BRM static DAC register. (See Section K.)



- \* **BSDAC1** (8 bits)+**SBRM1** (4 bits): 12-bit PWM/BRM static DAC register. (See Section K.)
- \* **WDTCLR**: Watchdog-timer-clear register, no specific hardware but an address. Writing any value to WDTCLR will clear the watchdog timer.
- \* **ADC**: Result of the A-to-D conversion.
- \* **HFCOUNTL**: Horizontal frequency counter register, low byte. (See Section L.d.)
- \* **HFCOUNTH**: Horizontal frequency counter register, high byte. (See Section L.d.)
- \* **VFCOUNTL**: Vertical frequency counter register, low byte. (See Section L.d.)
- \* **VFCOUNTH**: Vertical frequency counter register, high byte. (See Section L.d.)
- \* **PORT4**: Latch outputs (output only).
- \* **SOAREG**: Safe-Operation-Area register. (See Section L.g.)
- \* **SOACL**: Safe-Operation-Area Clear register, no specific hardware but an address. Writing anyvalue to SOACL will clear the SOA output (P1.5).
- \* **S1CON**: Serial Port 1 Control Register.
- \* **S1STA**: Serial Port 1 Status Register.
- \* **S1DAT**: Serial Port 1 Data Register.
- \* **S1ADR**: Serial Port 1 Address Register.

## B. 16K Bytes Flash Memory

Programming the Flash memory will be described in section F.

## C. 256 Bytes of On-Chip Data Memory

This data memory is mapped to external locations 00H to FFH and can only be accessed by the "MOVX @Ri" instruction. Since no external data can be accessed by this chip, there is no need for the external memory read/write control signals ( $\overline{RD}$ ,  $\overline{WR}$ ) as the "MOVX @Ri" instruction can only be executed internally.

## D. SPI (Synchronous Peripheral Interface) and RS232 Port: Serial Port 0

P3.0(RXD) and P3.1(TXD) can be used as a SPI port (serial port mode 0 of standard 80C51) or a RS232 port (mode 1, 2 or 3).

- The SPI port can be used to communicate to OSD chip, DAC ...
- An RS232 port can be used to talk to auto-alignment system, by using an 18.432 MHz crystal, aximun baud rate is 19200 bpS.

## E. DDC Port (support DDC1/2B/2B+, with two slave address registers)

- One DDC1 port to support DDC1
- One I2C port support DDC2B/2B+: Serial Port 1

An Interrupt is generated when DSCL has a transition from high to low and then remains low for 12 clock periods.



	16 MHz	18.432 MHz	20 MHz	24 MHz
<b>DSCL Low</b>	750 nS	651 nS	600 nS	499 nS

## F. I<sup>2</sup>C Port: Serial Port 2

(S/W emulation).

## G. Interrupts

The W78E354 has 6 interrupt sources. Five of them, with the exception of  $\overline{\text{INT1}}$  (at vector address 0013H) are identical to those of the 8051 series. The remaining one (at vector address 002BH) is a new addition. All the interrupt sources and the corresponding interrupt vector addresses for the W78E354 are given in the following table:

	SOURCE	VECTOR ADDRESS	DESCRIPTION	PRIORITY WITHIN A LEVEL
1	IE0	0003H	Same as the 8051.	Highest
2	TF0	000BH	Same as the 8051.	
3	*1	0013H	Replaces $\overline{\text{INT1}}$ of the 8051.	
4	TF1	001BH	Same as the 8051.	
5	RI+TI	0023H	Same as the 8051.	
6	*2	002BH	New addition. (like TF2 + EXF2 in the 8052)	Lowest

Notes:

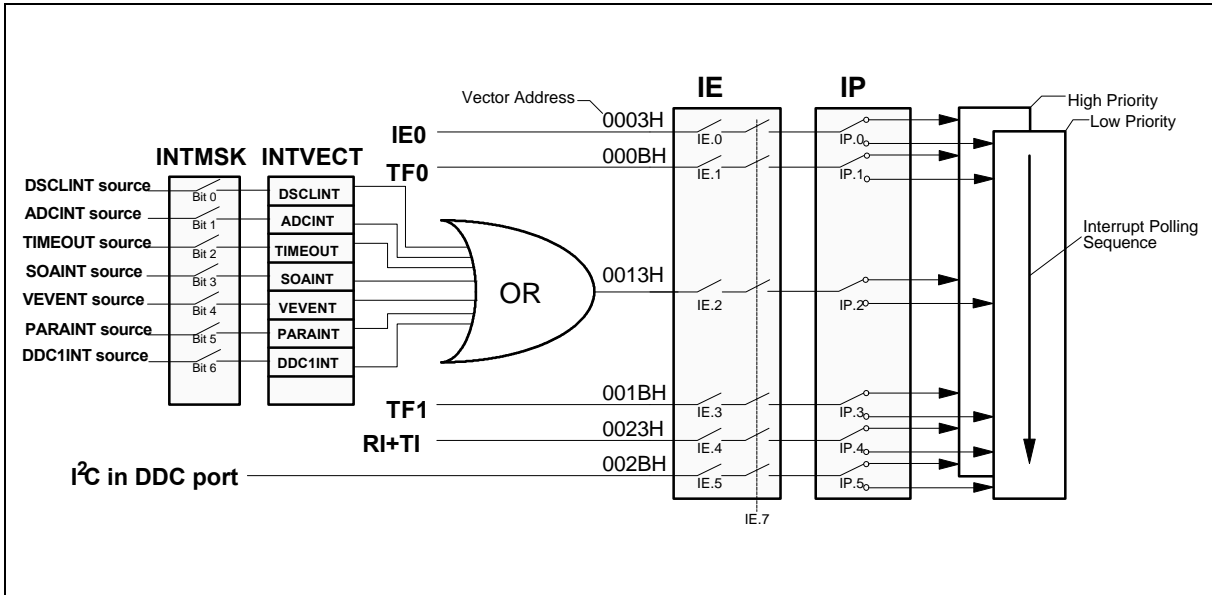
\*1 = DSCLINT + ADCINT + TIMEOUT + SOAINT + VEVENT + PARAINIT + DDC1INT.

\*2 is the interrupt generated by the I<sup>2</sup>C in the DDC port.

The interrupt at vector address 0013H is driven by another seven different sources. These are 1) a High-to-low transition of the DSCL-pin, 2) the A/D converter, 3) the Auto-reload Timer, 4) the SOA output, 5) Vsync, 6) the Parabola interrupt generator, and 7) DDC1 in the DDC port. The programmer must read the INTVECT register to identify the interrupt request source. These seven sources can be masked individually by setting the corresponding bit within the INTMSK register (Bit0..6). The newly added interrupt at vector address 002BH is driven by the I<sup>2</sup>C circuit in the DDC port.

The interrupt enable control bits for the two interrupts at 0013H and 002BH are the bits IE.2 and IE.5 in the IE register, respectively. They can be disabled by clearing IE.7 (disable all interrupts). The interrupt priority control bits are IP.2 and IP.5 in the IP register, respectively.

The following diagram illustrates the above description.



**H. 8-bit Auto-reload Timer for Software Time Base**

This is an 8-bit auto-reload timer, which generates a periodic interrupt to the CPU.

The time interval is programmable:

The minimum interval (unit) =  $1 / (F_{\text{clock}} \div 1024)$ ,

the programmable interval = the minimum interval  $\times$  (AUTOLOAD Reg. value + 1),

the maximum interval = the minimum interval  $\times$  255.

	16 MHz	18.432 MHz	20 MHz	24 MHz
Minimum Interval	64 $\mu$ S	55 $\mu$ S	51.2 $\mu$ S	42.6 $\mu$ S
Maximum Interval	16.3 mS	14.2 mS	13.1 mS	10.9 mS

**I. Parabola interrupt generator**

This is an 16-bit auto-reload timer, which generates a periodic interrupt to the CPU. The interrupt period is programmable: the time base =  $1/F_{\text{clock}}$ , the programmable interrupt period = the time base  $\times$  ([PARAH, PARAL] 16-bit Reg. value+1), the maximum period = the time base  $\times$  65535.

**J. 6-bit ADC**

One 6-bit Analog-to-Digital Converter.

SPEC.:

- $\pm 1$  LSB



- Conversion time:  $<150 \times 12/F_{osc}$  sec.
- 4 channels selected by an analog multiplexer

(ADCS1, ADCS0)	(0, 0)	(0, 1)	(1, 0)	(1, 1)
Selected Channel	ADC0	ADC1	ADC2	ADC3

Set bits ADCS1 and ADCS2 in CONTREG1 to select one of the four analog input channels. The ADC conversion is started by setting bit ADCSTRT in CONTREG1 using software. When the conversion is complete, the ADCSTRT bit is cleared by hardware to stop the ADC operation. The ADCINT bit in INTVECT is set by hardware at the same time.

### K. PWM DACs

There are two/teen 12/8-bit PWM SDACs and one/three 12/8-bit PWM DDACs in this chip. All the DAC output buffers have slew rate control to prevent the slew rate from being too large. Additionally, their outputs are delay-controlled and divided into three groups with different delay times as follows:

1. Delay about 5ns: BSDAC1, SDAC2, 5, 8, 11, DDAC1.
2. Delay about 10ns: SDAC0, 3, 6, 9, 12, DDAC2.
3. No delay: for the others.

### Functional Descriptions:

#### a. 14 channels of 8-bit Static DAC

The Static DACs are used to generate DC voltages (0–5V). There are 14 registers each corresponding to one 8-bit PWM 14 channel outputs. Unused PWM channels can be used as a standard output pin, as these pins can supply 0V or 5V.

- The duty cycle of the PWM output = Register value  $\div$  255
- The DC voltage after the low pass filter =  $V_{CC} \times$  duty cycle

REG. VALUE	DUTY CYCLE	DC VOLTAGE
0	0/255	0V
1	1/255	$1/255 \times 5V$
n	n/255	$n/255 \times 5V$
255	255/255	+5V

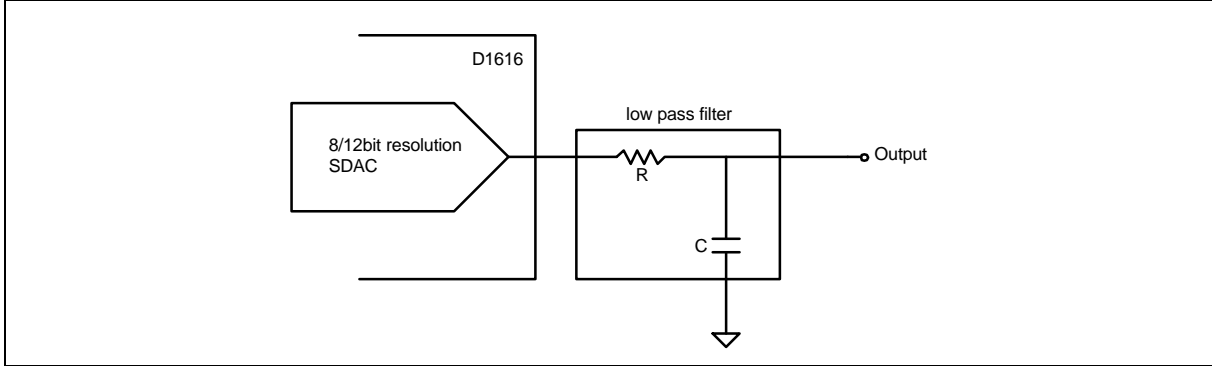
- The PWM frequency  $FPWM = F_{clock} \div 255$

	16 MHz	18.432 MHz	20 MHz	24 MHz
FPWM	62.745 KHz	72.282 KHz	78.431 KHz	94.117 KHz
TPWM	15.94 $\mu$ S	13.83 $\mu$ S	12.75 $\mu$ S	10.62 $\mu$ S





SDAC application circuit:



$$T = RC$$

$$V_{output} = V_{CC} \times n/255, \text{ if } T \gg TPWM$$

**b. 2 channels of 12-bit Static DAC**

The two channel, 12-bit PWM outputs are composed of an 8-bit PWM and a 4-bit BRM (Bit Rate Multiplier). The 4-bit BRM Reg. value decides which one is to be added one clock preiod in every 16 PWM outputs.

BRM Reg. 4-bit data	One clock period is incremented in the n-th output in every 16 PWM outputs.
0000	None
0001	n = 8
0010	n = 4, 12
0100	n = 2, 6, 10, 14
1000	n = 1, 3, 5, 7, 9, 11, 13, 15

Note: See the positions marked with an "\*" in the following figure.

BRM	BRM Cycle																
	Reg. value	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
0001	-	-	-	-	-	-	-	-	-	*	-	-	-	-	-	-	-
0010	-	-	-	-	*	-	-	-	-	-	-	-	*	-	-	-	-
0100	-	-	*	-	-	-	*	-	-	-	*	-	-	-	*	-	-
1000	-	*	-	*	-	*	-	*	-	*	-	*	-	*	-	*	-

Example:

0000	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
0011	-	-	-	-	*	-	-	-	*	-	-	-	*	-	-	-	-
1111	-	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*	*

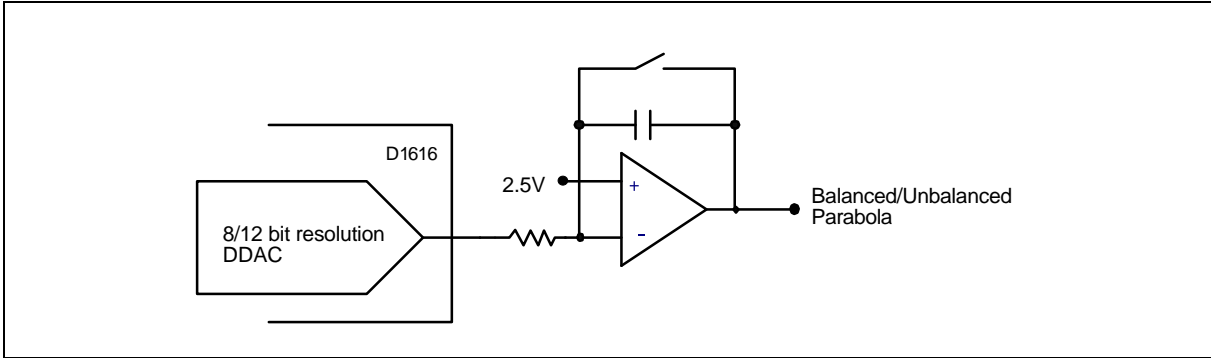
The 12-bit PWM frequency is the same as that of the 8-bit PWM output.



c. 1 channel of 12-bit & 3 channels of 8-bit Dynamic DAC


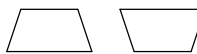

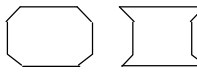
The Dynamic DACs are used to generate a parabola waveform for geometric compensation.

DDAC application circuit:



**Geometry compensation parabola waveform:**

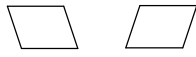
**DDAC0** can be used to compensate H size distortion:

- 1. PinCushion Correction (amplitude) (PCC amplitude) 
- 2. Trapezoid (Keystone) 
- 3. CBOW (S-comp) 
- 4. PinCushion correction (corner) (PCC corner) 

The PCC amplitude can be compensated against V size adjustment automatically.

The Trapezoid can be compensated against V center adjustment automatically.

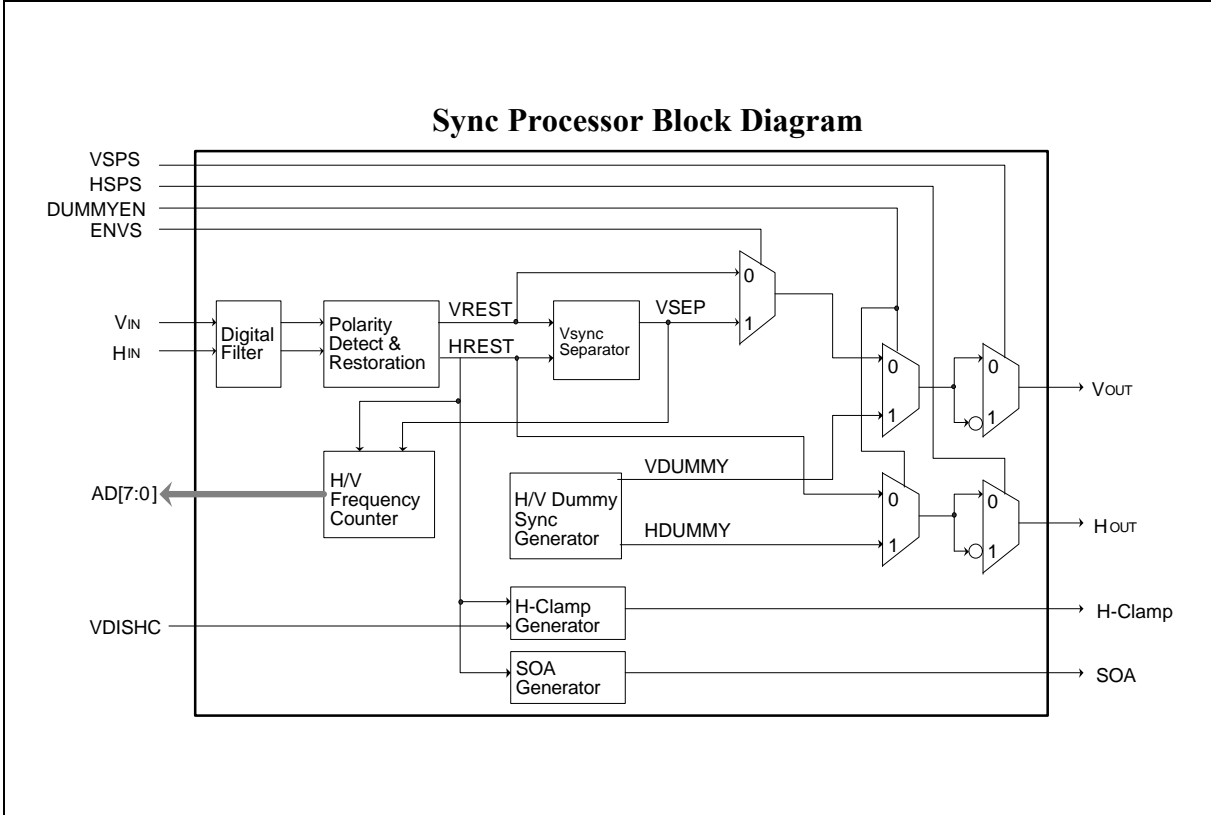
**DDAC1** is used to compensate H center distortion:

- 1. Pin balance (Bow) 
- 2. Key balance (Tilt) 

Note: The unused dynamic DACs can be used as static DACs.



L. Sync Processor



a. H/V Sync Digital Filter

Both Hsync and Vsync inputs have an internal digital filter to improve noise immunity. Any pulse that is shorter than an internal clock period will be regarded as a glitch and will be ignored.

Ex: Tclock = 62 nS @16 MHz, any sync with pulse width less than 62 nS will be regarded as a glitch.

b. Polarity Detector

The H/V polarity is detected automatically and can be read from the STATUS register, the H/V input signals are then polarity restored (become HREST/VREST) for internal processing and output to HOUT/VOUT to drive the deflection circuit.

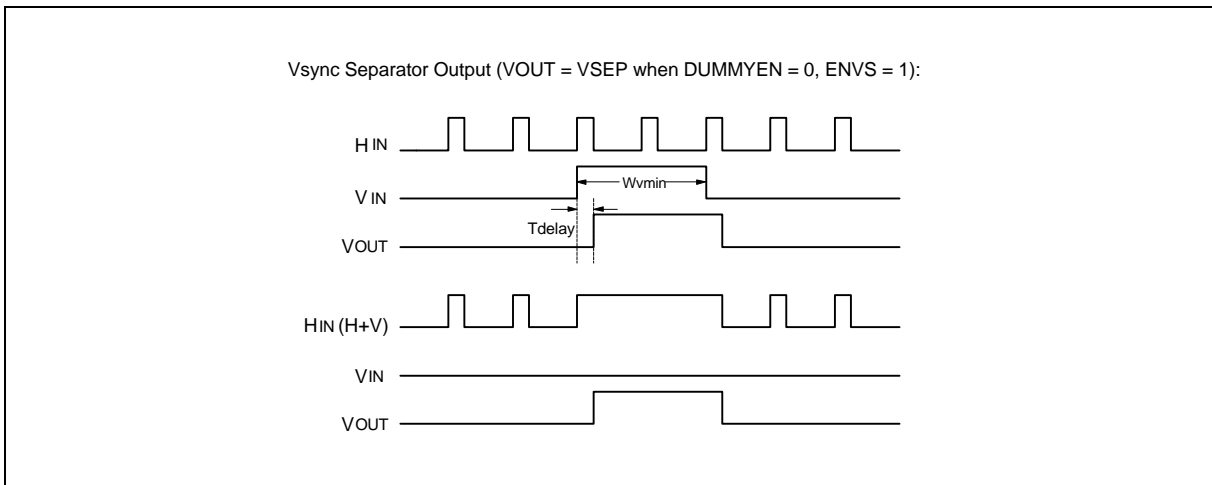
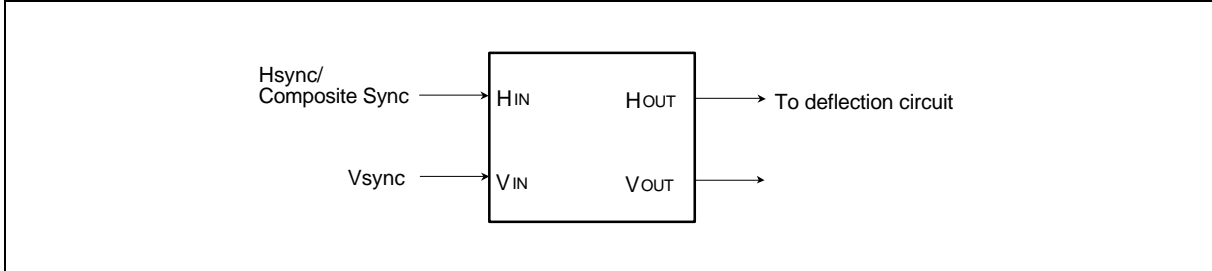
The maximum sync width to HIN pin is:  $(1/F_{clock}) \times 16384$

The maximum sync width to VIN pin is:  $(1/F_{clock}) \times 16384$

F <sub>CLOCK</sub>	16 MHz	18.432 MHz	20 MHz	24 MHz
Max. sync width for HIN	1024 μS	888 μS	819 μS	681 μS
Max. sync width for VIN	1024 μS	888 μS	819 μS	681 μS



c. Sync Separator



The Vsync is separated from the composite sync automatically, without any software effort.

The limitation for the Vsync signal is:

the VIN pulse width must be larger than  $W_{vmin} = (1/F_{clock}) \times 128.5, +/- 1/F_{clock} \div 2$

VOUT is also delayed from the VIN signal by  $T_{delay} = (1/F_{clock}) \times 128.5, +/- 1/F_{clock} \div 2$

(if ENVS bit is set to 1)

F <sub>CLOCK</sub>	16 MHz	18.432 MHz	20 MHz	24 MHz
1/F <sub>clock</sub>	62.5 nS	54 nS	50 nS	41 nS
Min. Vsync Width (W <sub>vmin</sub> )	8031 +/- 31 nS	6939 +/- 27 nS	6425 +/- 25 nS	5268 +/- 20 nS
VOUT Delay from VIN (T <sub>delay</sub> )	8031 +/- 31 nS	6939 +/- 27 nS	6425 +/- 25 nS	5268 +/- 20 nS

d. Horizontal & Vertical Frequency Counter

There are two 16-bit counters which can count H and V frequency automatically. When a VEVENT (V frequency counter timeout) interrupt occurs, the MCU may read the count value (Hcount and Vcount) from the counter registers (HFCOUNTH, HFCOUNTL, VFCOUNTH and VFCOUNTL) to calculate the H and V frequency by the formulas listed below.



**V frequency:**

The resolution of V frequency counter:  $V_{resol} = (1/F_{clock}) \times 16$ .

The V frequency:  $V_{freq} = 1/(V_{count} \times V_{resol})$ .

The lowest V frequency can be detected:  $F_{clock} \div 1048576$ .

**H frequency:**

The resolution of H frequency counter:  $H_{resol} = (1/F_{clock}) \div 8$ .

The H frequency:  $H_{freq} = 1/(H_{count} \times H_{resol})$ .

The lowest H frequency can be detected:  $F_{clock} \div 8192$ .

	16 MHz	18.432 MHz	20 MHz	24 MHz
Vresol	1 $\mu$ s	868 nS	800 nS	666 nS
The Lowest Vfreq	15 Hz	17.6 Hz	19 Hz	23 Hz
Hresol	7.8 nS	6.8 nS	6.3 nS	5.2 nS
The Lowest Hfreq	1.9 KHz	2.3 KHz	2.4 KHz	2.9 KHz

e. Dummy Frequency Generator

The Dummy H and V frequencies are generated for 1) factory burn-in and 2) displaying warning messages if there is no input frequency.

There are two registers in the dummy sync generator:

DHREG: 4-bit register, determines the Dummy Hsync output frequency

DVREG: 8-bit register, determines the Dummy Vsync output frequency

Dummy Hsync frequency  $F_{dH} = F_{clock} \div 32 \div (DHREG+1)$

Dummy Vsync frequency  $F_{dV} = F_{dH} \div 8 \div (DVREG+1)$

DUMMYEN	Hout	Vout
0	HREST	VREST (if ENVS = 0), VSEP (if ENVS = 1)
1	HDUMMY	VDUMMY

Ex. If System clock = 16 MHz

DHREG	F <sub>dH</sub>	DVREG	F <sub>dV</sub>
15	31.25K	48	79.7 Hz
12	38.5K	59	80.2 Hz
10	45.5K	70	80.1 Hz
9	50K	77	80.1 Hz
7	62.5K	96	80.5 Hz
6	71K	109	80.7 Hz
5	82K	127	80.1 Hz
4	100K	155	80.1 Hz



**f. H-clamp Pulse Generator**

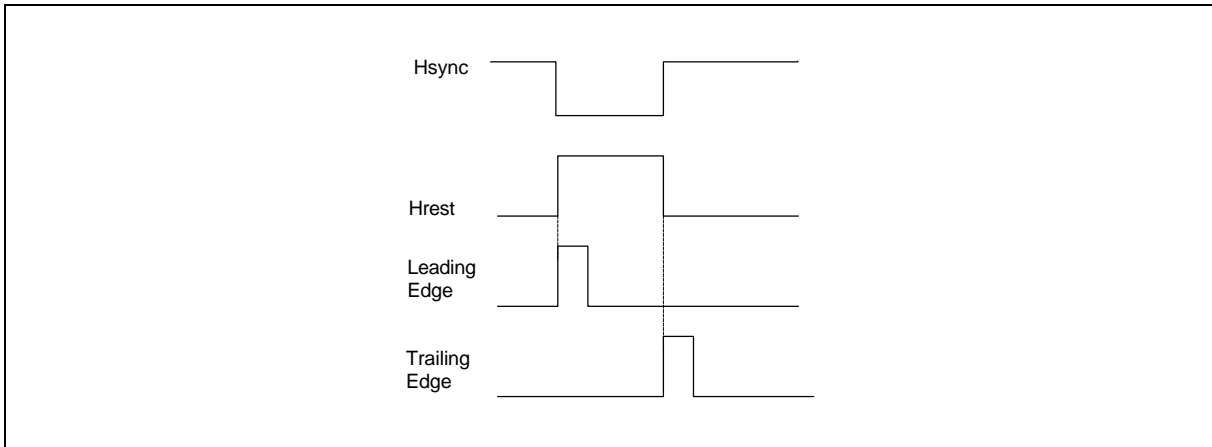
If P14SF = 0, P1.4 is a general purpose I/O port.

If P14SF = 1, P1.4 is the H-clamp pulse output.

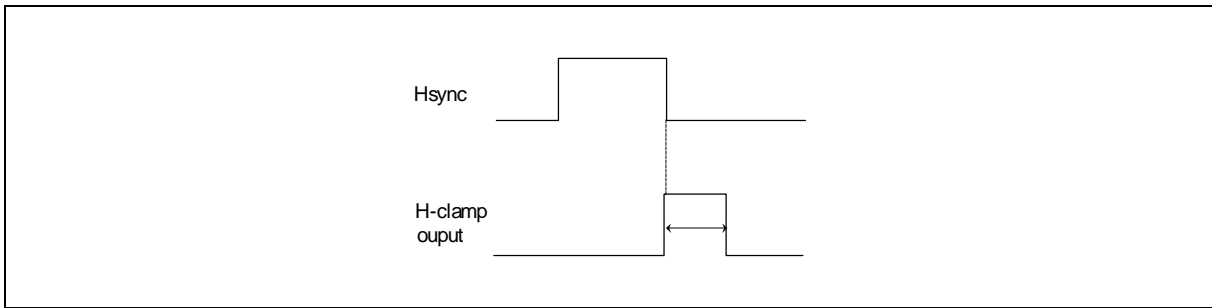
1. Leading edge / Trailing edge selectable

HCES = 0: select leading edge

HCES = 1: select trailing edge



2. Pulse width selectable



The pulse width is programmable:  $(1/F_{clock}) \times \text{Option}, \pm 1/F_{clock} \div 2$

(HCWS1, HCWS0)	OPTION	16 MHz	18.432 MHz	20 MHz	24 MHz
(0, 0)	4.5	281 +/- 31 nS	244 +/- 27 nS	225 +/- 25 nS	187 +/- 20 nS
(0, 1)	8.5	531 +/- 31 nS	461 +/- 27 nS	425 +/- 25 nS	353 +/- 20 nS
(1, 0)	16.5	1031 +/- 31 nS	896 +/- 27 nS	825 +/- 25 nS	686 +/- 20 nS
(1, 1)	32.5	2031 +/- 31 nS	1764 +/- 27 nS	1625 +/- 25 nS	1352 +/- 20 nS

**g. SOA output**

If P15SF = 0, P1.5 is a general purpose I/O port.

If P15SF = 1, P1.5 is the SOA output.



**Purpose:**

To protect the HOT (Horizontal Oscillating Transistor) and other critical circuitry by making a quick response when the Hsync frequency drops below the preset boundary frequency.

**Operation:**

When the Hsync frequency is lower than the boundary frequency for three consecutive cycles or stopped for a certain period, the SOA pin (P1.5) will change to a "high" state (for the external protection circuit to function). Writing any value to the SOACLR register will release the SOA pin.

To set the boundary frequency, one can write some formula: value to the SOAREG register according to the SOAREG value =  $2M \div \text{boundary frequency}$

Ex: If 50 KHz is considered the boundary frequency, then  $SOAREG = 2M \div 50K = 40$ .

No Hsync response time =  $2048 \times (1/F_{\text{clock}})$ .

	16 MHz	18.432 MHz	20 MHz	24 MHz
No H response time	128 $\mu$ S	110 $\mu$ S	102 $\mu$ S	85 $\mu$ S

**M. Power Supervisor, Watchdog Timer and Reset Circuitry**

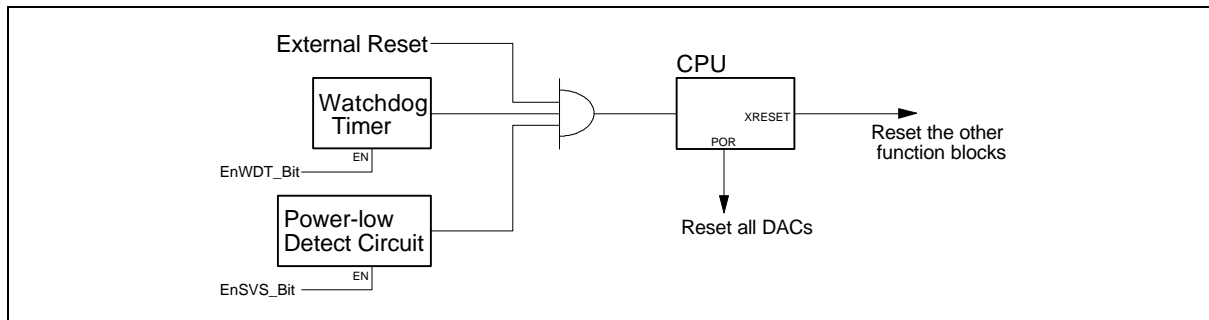
The reset signals come from the following three sources:

1. External reset input (active low)
2. Power low detect
3. Hardware Watchdog Timer

The power-low detection circuit generates a reset signal once the Vcc voltage falls below 3.8V. This reset signal is released a short time after Vcc has increased above 4.3V. This function can be enabled or disabled by a code option.

The purpose of a watchdog timer is to reset the CPU if it enters erroneous processor states (possibly caused by electrical noise or RFI) within a reasonable period of time. The watchdog timer clock source comes from the internal system clock and can be enabled or disabled by a code option. When enabled, the watchdog circuitry will generate a system reset if the user program fails to reload the watchdog timer (by writing any value to the WDTCLR register) within a specified length of time known as the "watchdog interval". The watchdog interval has four code options:  $219/f_{osc}$ ,  $221/f_{osc}$ ,  $223/f_{osc}$  and  $224/f_{osc}$  sec.

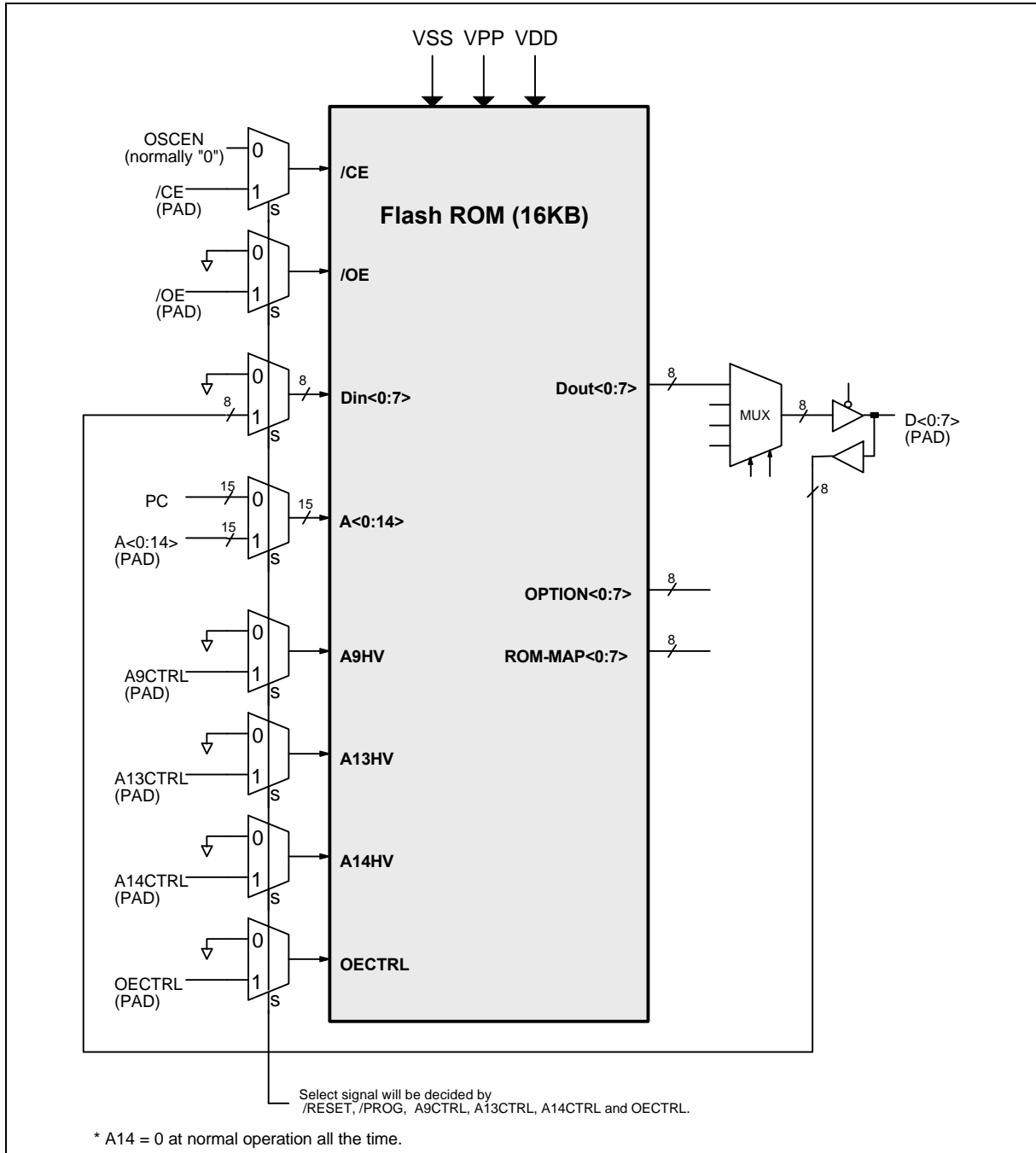
The block diagram of the reset circuitry is shown as follows:



## FLASH CELL DESCRIPTION

### A. Flash ROM Interface

The following diagram shows the Flash cell block control interface. A<0:14> are the address bus inputs and Dout<0:7> are the data bus outputs of the Flash ROM.



Flash ROM Block Diagram

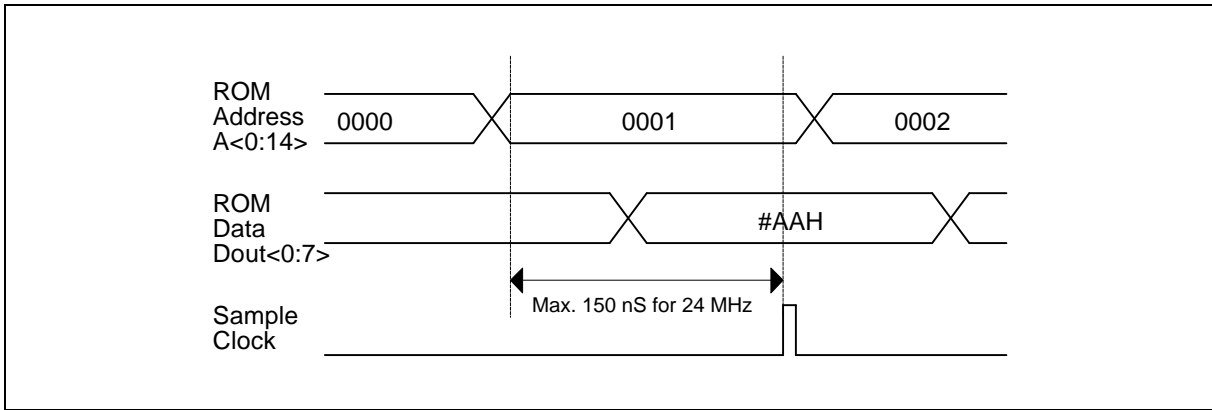




**V<sub>PP</sub>** is the high voltage input while in Flash Mode. **A<0:14>** is the address bus of the Flash cell while in Flash Mode. **Dout<0:7>** is the data bus output of the Flash cell and **Din<0:7>** is the data bus input while the chip is in Flash mode. The **A9CTRL**, **A13CTRL**, **A14CTRL** and **OCTRL** signals are used to select the Flash Mode. The **OE** and **CE** signals are the control strobe signals for Flash Mode operation. These signals are operational only in Flash Mode and appear as inputs/outputs via the external pins with a "Test Name" as listed in the Pin Description in Sec. D.

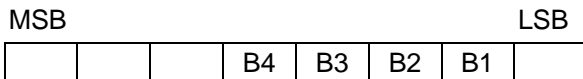
During normal operation, the critical timing parameter is the Flash data access time. When operating at 24 MHz, the Flash cell requires 150 nS after an address out until the data is valid, as shown below.

**Timing for Flash ROM Data Access**



**B. Option Setting Bits**

The **Option setting bits** are used to set user-selectable options. These bits are programmed in the same way as the 16K byte Flash ROM except for the address A<14:0> which is 7FFFH.



Note: Default value is 1 for each bit.

- **B1: EnWDT\_Bit.** (1: Disable, 0:Enable)  
This bit is used to enable/disable the Watchdog Timer operation.
- **(B3, B2): WatchDog Timer period set.**  
These two bits are used to set the time period of the Watchdog timer.
  - (0, 0): 219/fosc sec.
  - (0, 1): 221/fosc sec.
  - (1, 0): 223/fosc sec.
  - (1, 1): 224/fosc sec.
 Where fosc is the crystal frequency.
- **B4: EnSVS\_Bit.** (1: Disable, 0:Enable)  
This bit is used to enable/disable the Power-low-detection function.



## C. ROM-MAP Bits

In order to increase the functionality of the 16K byte Flash ROM, the Flash ROM is divided into 4 blocks. If some blocks contain bad Flash cells but the other blocks are good, the 16KB Flash can be treated as either 8KB or 4KB, and the W78E354 downgraded to either the W78E352 or the W78E351.

Four ROM-MAP bits are used to indicate the availability of the 16K bytes of Flash ROM after testing.



	16K bytes Flash ROM
Set B0 = 1 if block 0 is available.	Block 0, 4K bytes
Set B1 = 1 if block 1 is available.	Block 1, 4K bytes
Set B2 = 1 if block 2 is available.	Block 2, 4K bytes
Set B3 = 1 if block 3 is available.	Block 3, 4K bytes

Note: Only one/two/four of the four bits can be set to indicate whether 4K/8K/16K are usable.

## FLASH/TEST MODE

### A. Flash Modes

#### 1. Read

This mode is supported for customer code verification. The data will be invalid if the Lock bit is set low.

#### 2. Output Disable

When the  $\overline{OE}$  is set high, no data outputs appear on D7..D0.

#### 3. Standby

This condition disables the DC path from the Flash cell to reduce power consumption.

#### 4. Program

This mode is used to program the Flash cell and option bits. It is the only way to change data from "1" to "0".

#### 5. Program Verify

All the programming data must be checked after program or mass program operations. This operation should be performed after each byte is programmed to ensure a substantial program margin.

#### 6. Erase

An erase operation is the only way to change data from "0" to "1".

#### 7. Erase Verify

After an erase operation, all of the bytes in the chip must be verified to check whether they have been successfully erased to 1 or not. The erase verify operation automatically ensures a substantial erase margin. This operation will be implemented after the erase operation if  $V_{PP} = V_{EP}$  (14.5V),  $\overline{CE}$  is high and  $\overline{OE}$  is low.



### 8. Proram/Erase Inhibit

This operation allows parallel erasing or programming of multiple chips with different data.

### 9. Mass Program

In order to increase the throughput of testing, this operation programs 256 bytes with the same data simultaneously. Note that 256 program verify operations must follow each mass program operation. All the timings for this operation are the same as those of the byte program operation except that the /CE program pulse width is 125 $\mu$ S. In addition, this operation is also used for cell reliability analysis by stressing the source line.

### 10. Read Company ID and Device ID

These two modes are especially useful in EPROM WRITERS, which can read the silicon identification to set the appropriate erase or program algorithm to match the device being erased or programmed.

### 11. VT

This operation is used for cell performance analysis. By connecting 2V to the D7..D0 pins, the cell currents can be measured for each location within the chip by specifying its appropriate address.

### 12. Read ROM-map Bits

This operation is used to verify the ROM-MAP bits which were programmed previously. Its action is the same as an EEPROM read operation.

### 13. Fuse ROM-map Bits

The ROM-MAP bits can be fused by this operation only. Its action is the same as an EEPROM program operation.

### 14. Erase ROM-map Bits

The ROM-MAP bits can be erased by this operation only. Its action is the same as an EEPROM erase operation.

### 15. CKBD & /CKBD Mass Program

These two operations are used to mass program the Flash cells in such a way that the state of any bit is different from those of its neighboring bits.

### 16. Read Disturb

## B. Test Mode

#### \*RAM-test Mode

This mode is used to verify the function of the internal 512 bytes of RAM by a write-in and then read-out operation.

#### \*Functional Test Mode

If the  $\overline{\text{EA}}$  (TestCLK) pin is pulled low when the chip is being reset and remains low for at least 24 clock periods after the reset, the CPU will execute from the external program memory (maximum program size is 2K bytes). This feature may be used to test the chip's functions via an external program. It should be noted that this mode is like the normal operation except that the CPU executes from external program memory and that some different pins are used in place of A10–A0, D7–D0 and  $\overline{\text{PSEN}}$  instead of their original functions.



Flash/RAM-test Mode Configuration Table.

CONFIGURATION									
Flash Modes	A9CTRL	A13CTRL	A14CTRL	OECTRL	/CE	/OE	VPP	A14..A0	D7..D0
Read	0	0	0	0	0	0	1	Address	Data Out
Output Disable	0	0	0	0	0	1	1	X	High-Z
Standby	0	0	0	0	1	X	1	X	High-Z
Program	0	0	0	0	0	1	VCP	Address	Data In
Program Verify	0	0	0	0	1	0	VCP	Address	Data Out
Erase [*3]	1	0	0	0	0	1	VEP	A0 = 0, others: X	Data In (FFh)
Erase Verify	1	0	0	0	1	0	VEP	Address	Data Out
Program/Erase Inhibit	0	0	0	0	1	1	VCP/VEP	X	X
Mass Program	0	0	1	0	0	1	VCP	X	Data In
Read Company ID	1	0	0	0	0	0	1	A0 = 0, others: X	Data Out (DAh)
Read Device ID								A0 = 1, others: X	Data Out (64h)
VT	0	0	0	1	0	1	1	Address	Cell Current
Read ROM-MAP	0	1	0	0	0	0	1	7FFFh	Data Out
Fuse ROM-MAP	0	1	0	0	0	1	VCP	7FFFh	Data In
Erase ROM-MAP	1	1	0	0	0	1	VEP	X	Data In (FFh)
CKBD & /CKBD Mass Program	1	0	1	0	0	1	VCP	A6, A0 [*4]	Data In (00h)
Read Disturb	1	1	1	0	0	0	1	Address	Data Out

CONFIGURATION											
RAM-test Modes	A9CTRL	A13CTRL	A14CTRL	OECTRL	/CE	/OE	VPP	A14..A9	A8	A7..A0	D7..D0
8032's 256 bytes of RAM-write	0	1	1	X	0	1	X	X	0	Address	Data In
8032's 256 bytes of RAM-read	0	1	1	X	1	0	X	X	0	Address	Data Out
Data Memory by MOVX-write	0	1	1	X	0	1	X	X	1	Address	Data In
Data Memory by MOVX-read	0	1	1	X	1	0	X	X	1	Address	Data Out

Notes:

- 1: RESET and PROG must be kept low for all the above modes.
- 2: "X" means "Don't care" but not floating. VCP = 12.5V, VEP = 14.5V, "1" stands for VDD and "0" for Vss.
- \*3: The Erase operation erases all the 16K bytes of Flash cell but not the ROM-MAP cell.
- \*4: A0/A6 decides whether the bit-line/word-line is even or odd.



For CKBD, (A6, A0) = (0, 0) and then (1, 1); for /CKBD, (A6, A0) = (1, 0) and then (0, 1).

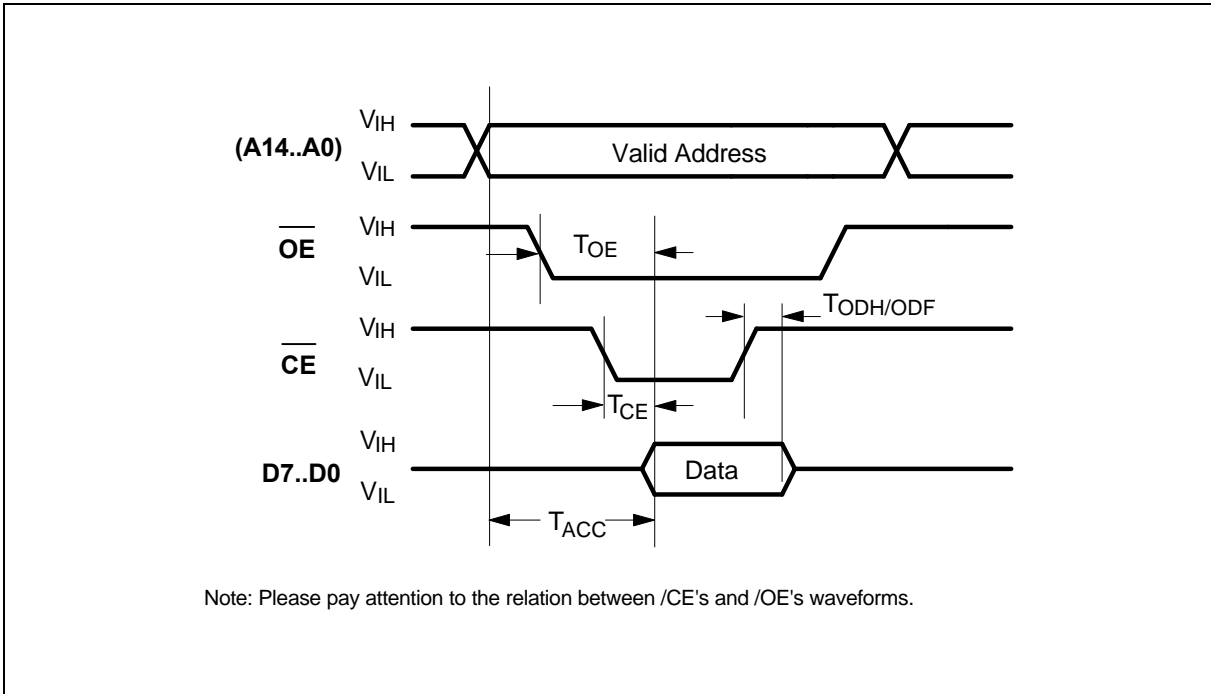
**G.3 Flash Mode Timing Waveforms**

**\*Read Operation**

(including EEPROM, Company ID, Device ID, Option bits and ROM-MAP bits Read)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Address Access Time	T <sub>ACC</sub>	-	-	150	nS
Chip Enable Access Time	T <sub>CE</sub>	-	-	150	nS
Output Enable Access Time	T <sub>OE</sub>	-	-	150	nS
Output Data Hold Time	T <sub>ODH</sub>	0	-	-	nS
Output Data Float Time	T <sub>ODF</sub>	-	-	100	nS

**Read Waveform**



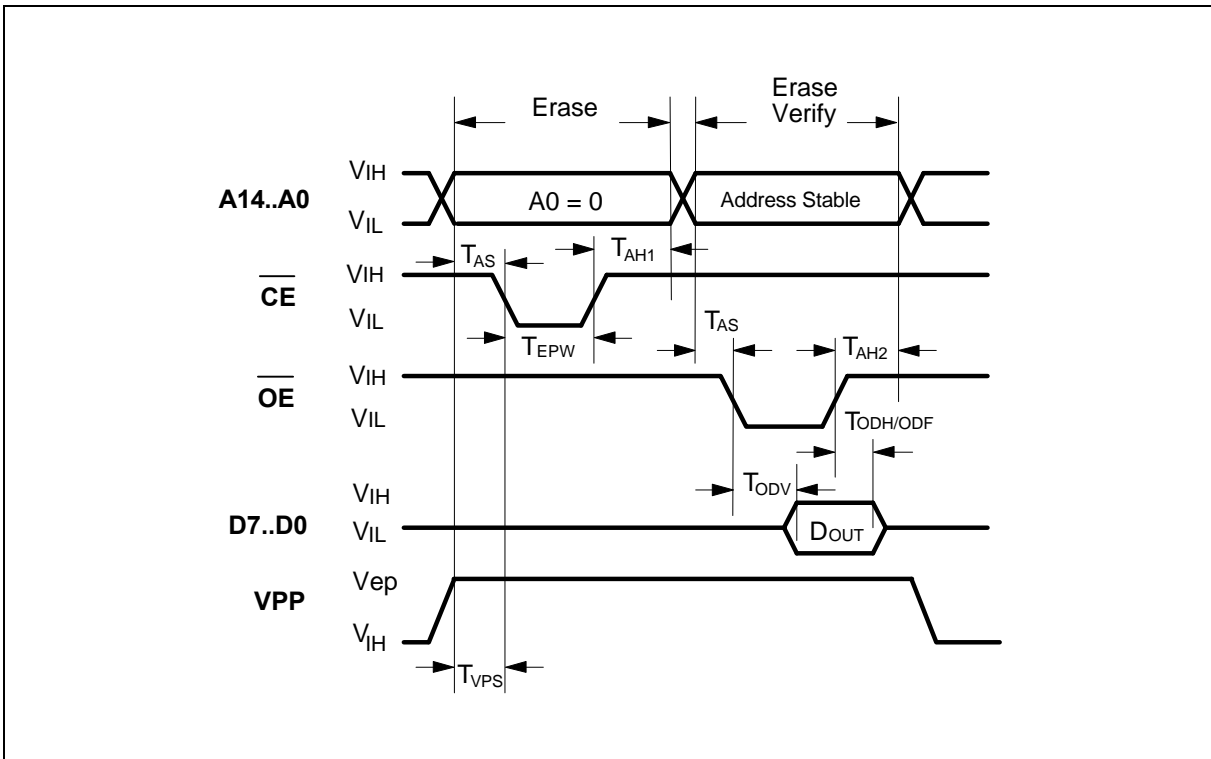


**\*Erase Operation**

(including EEPROM&Option bits and ROM-MAP bits Erase)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Vpp Setup Time	TVPS	2.0	-	-	μS
Address Setup Time	TAS	2.0	-	-	μS
Address Hold Time	TAH1	2.0	-	-	μS
Erase Pulse Width	TEPW	-	1	5	mS
Output Data Valid after $\overline{OE}$ Low	TODV	-	-	150	nS
Address Hold Time	TAH2	0	-	-	μS
Output Data Hold Time	TODH	0	-	-	nS
Output Data Float Time	TODF	-	-	100	nS

**Erase Waveform**



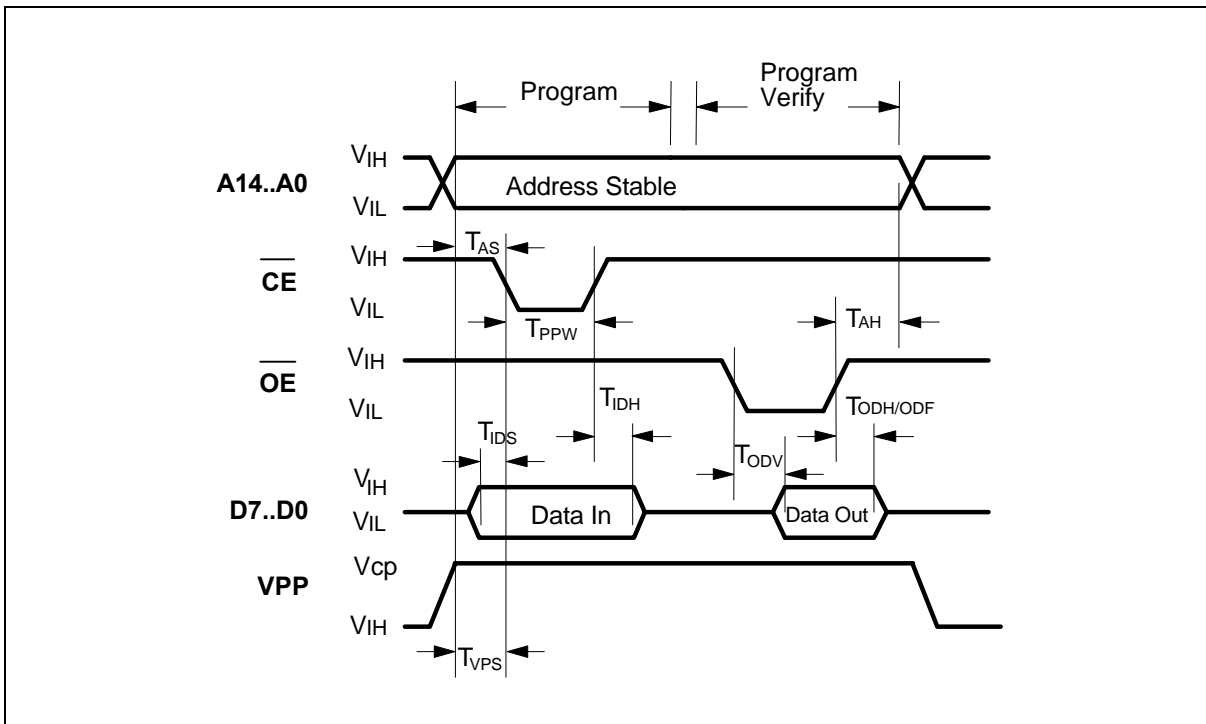


**\*Program & Mass Program Operation**

(including EEPROM, Option bits and ROM-MAP bits Program, and Mass Program)

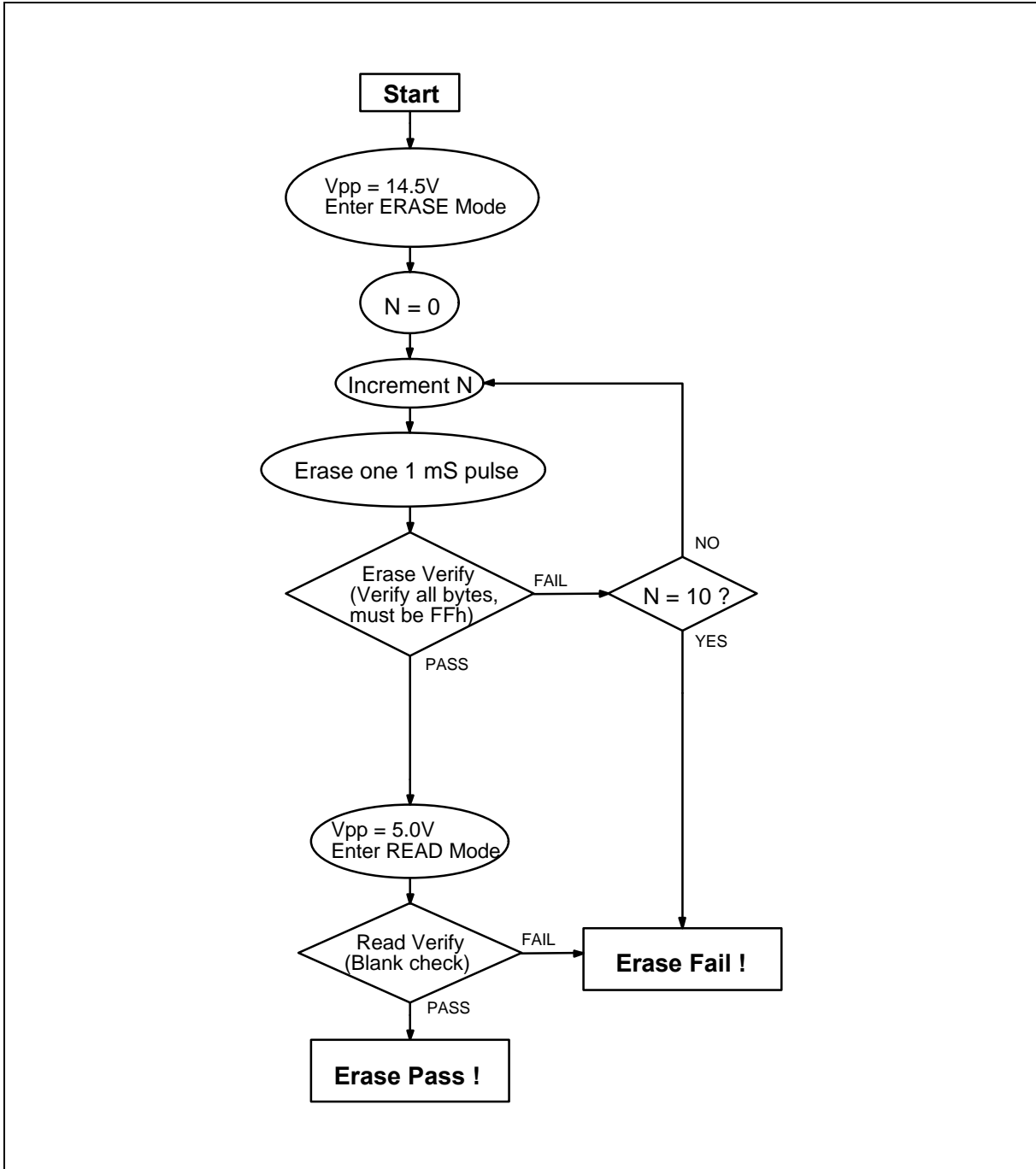
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Vpp Setup Time	T <sub>VPS</sub>	2.0	-	-	μS
Address Setup Time	T <sub>AS</sub>	2.0	-	-	μS
Input Data Setup Time	T <sub>IDS</sub>	2.0	-	-	μS
Input Data Hold Time	T <sub>IDH</sub>	2.0	-	-	μS
Program Pulse Width	T <sub>PPW</sub>	-	100	200	μS
Mass Program Pulse Width	T <sub>MPPW</sub>	-	500	1000	mS
Output Data Valid after $\overline{OE}$ Low	T <sub>ODV</sub>	-	-	150	nS
Address Hold Time	T <sub>AH</sub>	0	-	-	μS
Output Data Hold Time	T <sub>ODH</sub>	0	-	-	nS
Output Data Float Time	T <sub>ODF</sub>	-	-	100	nS

**Program Waveform**





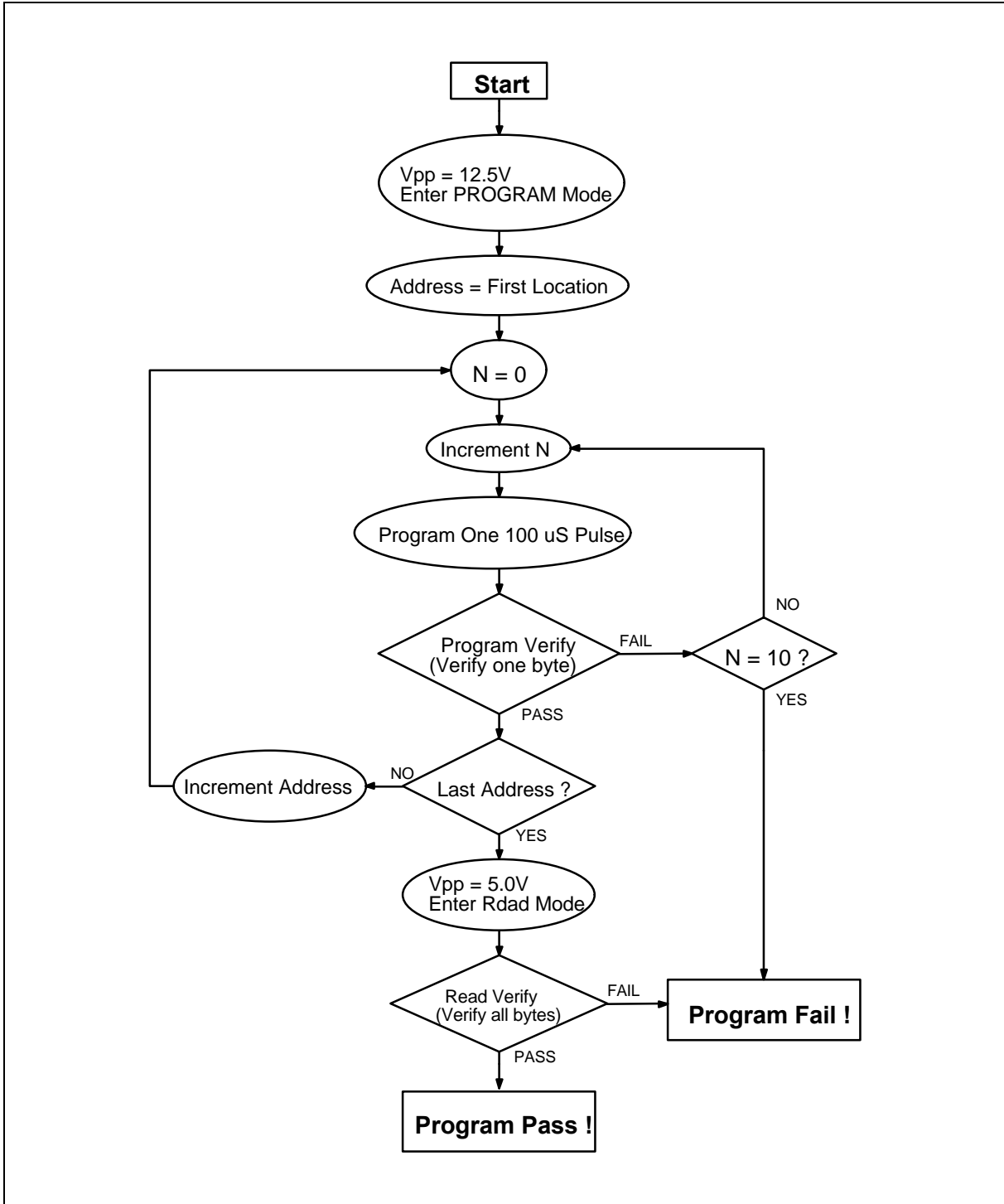
D.1 Smart Erase Algorithm







D.2 Smart Program Algorithm





## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
DC Power Supply	V <sub>DD</sub>	-0.3	+7.0	V
Input Voltage	V <sub>IN</sub>	V <sub>SS</sub> -0.3	V <sub>DD</sub> +0.3	V
Input Current	I <sub>I</sub>	-100	+100	mA
Operating Temperature	T <sub>A</sub>	0	70	°C
Storage Temperature	T <sub>ST</sub>	-55	150	°C

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

## ELECTRICAL CHARACTERISTICS

### Normal Operation D.C. Characteristics

(V<sub>DD</sub> & V<sub>AA</sub>)–V<sub>SS</sub> = 5V ±10%, T<sub>A</sub> = 25°C, F<sub>osc</sub> = 20 MHz, unless otherwise specified.

PARAMETER	SYM.	SPECIFICATION			UNIT	TEST CONDITIONS
		Min.	Typ.	Max.		
Operating Voltage	V <sub>DD</sub>	4.5	5	5.5	V	
Operating Current	I <sub>DD</sub>	-	-	65	mA	No load, V <sub>DD</sub> = 5.5V
Idle Current	I <sub>IDLE</sub>	-	-	30	mA	No load, V <sub>DD</sub> = 5.5V
Power-down Current	I <sub>PD</sub>	-	-	10	μA	No load, V <sub>DD</sub> = 5.5V
<b>Inputs</b>						
Logic 0 Input Current P1, P2, P3 (except P1.0–P1.3, P1.5)	I <sub>IN1</sub>	-75	-	-10	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 0V
Input Current $\overline{\text{RESET}}$ , TestCLK (*1)	I <sub>IN2</sub>	-250	-	-	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 0V
Input Current H <sub>IN</sub> , V <sub>IN</sub> (*2)	I <sub>IN3</sub>	-	-	+30	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = V <sub>DD</sub>
Input Leakage Current P1.0–P1.3, ADC0–ADC3	I <sub>LK</sub>	-10	-	+10	μA	V <sub>DD</sub> = 5.5V 0V < V <sub>IN</sub> < V <sub>DD</sub>
Logical 1-to-0 Transition Current P1, P2, P3 (*3) (except P1.0–P1.3, P1.5)	I <sub>TL</sub>	-650	-	-	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 2.0V



Normal Operation D.C. Characteristics, continued

PARAMETER	SYM.	SPECIFICATION			UNIT	TEST CONDITIONS
		Min.	Typ.	Max.		
Input Low Voltage (*4) P1, P2, P3 (except P1.0–P1.3, P1.5) RESET	V <sub>IL1</sub>	0	-	0.8	V	V <sub>DD</sub> = 4.5V
Input Low Voltage (*4) H <sub>IN</sub> , V <sub>IN</sub>	V <sub>IL2</sub>	0	-	0.8	V	V <sub>DD</sub> = 4.5V
Input Low Voltage (*4) P1.0–P1.3	V <sub>IL3</sub>	0	-	1.5	V	V <sub>DD</sub> = 4.5V
Input High Voltage P1, P2, P3 (except P1.0–P1.3, P1.5)	V <sub>IH1</sub>	2.4	-	V <sub>DD</sub> +0.2	V	V <sub>DD</sub> = 5.5V
Input High Voltage (*4) RESET, OSCIN	V <sub>IH2</sub>	3.5	-	V <sub>DD</sub> +0.2	V	V <sub>DD</sub> = 5.5V
Input High Voltage (*4) H <sub>IN</sub> , V <sub>IN</sub>	V <sub>IH3</sub>	2.4	-	V <sub>DD</sub> +0.2	V	V <sub>DD</sub> = 5.5V
Input High Voltage (*4) P1.0–P1.3	V <sub>IH4</sub>	3.0	-	V <sub>DD</sub> +0.2	V	V <sub>DD</sub> = 5.5V
<b>Outputs</b>						
Output Low Voltage P1.0, P1.1	V <sub>OL1</sub>	-	-	0.4	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +2 mA
Output Low Voltage P1.2, P1.3	V <sub>OL2</sub>	-	-	0.4	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +6 mA
Output Low Voltage P1.4, P1.5, P2.2–P2.7 SDAC0–13, H <sub>OUT</sub> , V <sub>OUT</sub>	V <sub>OL3</sub>	-	-	0.45	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +4 mA
Output Low Voltage P2.0, P2.1	V <sub>OL4</sub>	-	-	0.5	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +15 mA
Output Low Voltage P3, P4	V <sub>OL5</sub>	-	-	0.45	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +2 mA
Output Low Voltage BSDAC0–1, DDAC0–2, BDDAC	V <sub>OL6</sub>	-	-	0.45	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +8 mA



## Normal Operation D.C. Characteristics, continued

PARAMETER	SYM.	SPECIFICATION			UNIT	TEST CONDITIONS
		Min.	Typ.	Max.		
Output High Voltage P1.4, P2, P3	VOH1	2.4	-	-	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = -100 μA
Output High Voltage P4	VOH2	2.4	-	-	V	V <sub>DD</sub> = 4.5V I <sub>OH</sub> = -2 mA
Output High Voltage P1.5, SDAC0–13, HOUT, VOUT S.F. of P1.4 and P2.3–P2.7 <sup>(*5)</sup>	VOH3	2.4	-	-	V	V <sub>DD</sub> = 4.5V I <sub>OH</sub> = -4 mA
Output High Voltage BSDAC0–1, DDAC0–2, BDDAC	VOH4	2.4	-	-	V	V <sub>DD</sub> = 4.5V I <sub>OH</sub> = -8 mA

## Notes:

- \*1. RESET and TestCLK have an internal pull-up resistor of about 30 KΩ.
- \*2. H<sub>IN</sub> and V<sub>IN</sub> have an internal pull-down resistor of about 200 KΩ.
- \*3. P1, P2 and P3 (except P1.0–P1.3 and P1.5) can source a transition current when they are being externally driven from 1 to 0. The transition current reaches its maximum value when V<sub>IN</sub> is approximately 2V.
- \*4. P1.0–P1.3, RESET, H<sub>IN</sub> and V<sub>IN</sub> are Schmitt trigger inputs, and OSCIN is a CMOS input.
- \*5. While outputting a special function, the source current of P1.4 and P2.3–P2.7 is -4 mA.

## Flash Operation D.C. Characteristics

(V<sub>DD</sub> & V<sub>AA</sub>)–V<sub>SS</sub> = 5V ±10%, T<sub>A</sub> = 25°C, F<sub>osc</sub> = 20 MHz, unless otherwise specified.

PARAMETER	SYM.	SPECIFICATION			UNIT	TEST CONDITIONS
		MIN.	TYP.	MAX.		
Input Current A0–A14, D0–D7, A9CTRL, A13CTRL, A14CTRL, OCTRL, OE, CE	I <sub>IN</sub>	-75	-	+10	μA	V <sub>DD</sub> = 5.5V V <sub>IN</sub> = 0V or V <sub>DD</sub>
V <sub>PP</sub> Erase Current (V <sub>PP</sub> = V <sub>EP</sub> )	I <sub>EP</sub>	-	-	+200	μA	V <sub>DD</sub> = 5.5V CE = V <sub>IL</sub> , CE = V <sub>IH</sub>
V <sub>PP</sub> Program Current (V <sub>PP</sub> = V <sub>CP</sub> )	I <sub>CP</sub>	-	-	+200	μA	V <sub>DD</sub> = 5.5V CE = V <sub>IL</sub> , CE = V <sub>IH</sub>
Input Low Voltage A0–A14, D0–D7, A9CTRL, A13CTRL, A14CTRL, OCTRL, OE, CE	V <sub>IL</sub>	0	-	0.8	V	V <sub>DD</sub> = 4.5V



Flash Operation D.C. Characteristics, continued

PARAMETER	SYM.	SPECIFICATION			UNIT	TEST CONDITIONS
		MIN.	TYP.	MAX.		
Input High Voltage A0–A14, D0–D7, A9CTRL, A13CTRL, A14CTRL, OECTRL, $\overline{OE}$ , $\overline{CE}$	V <sub>IH</sub>	2.4	-	V <sub>DD</sub> +0.2	V	V <sub>DD</sub> = 5.5V
Output Low Voltage D0–D7	V <sub>OL</sub>	-	-	0.45	V	V <sub>DD</sub> = 4.5V I <sub>OL</sub> = +2 mA
Output High Voltage D0–D7	V <sub>OH</sub>	2.4	-	-	V	V <sub>DD</sub> = 4.5V I <sub>OH</sub> = -100 $\mu$ A
V <sub>PP</sub> Erase Voltage	V <sub>EP</sub>	14.25	14.5	14.75	V	
V <sub>PP</sub> Program Voltage	V <sub>CP</sub>	12.25	12.5	12.75	V	

## TYPICAL APPLICATION

Please note:

While the chip is being powered on and the  $\overline{RESET}$  pin is low, if P1.5 and P3.2 are kept low at the same time, then the POR (Power-on Reset) will last until P1.5 or P3.2 is pulled High, whichever occurs first.



### Headquarters

No. 4, Creation Rd. III,  
Science-Based Industrial Park,  
Hsinchu, Taiwan  
TEL: 886-3-5770066  
FAX: 886-3-5792697  
<http://www.winbond.com.tw/>  
Voice & Fax-on-demand: 886-2-27197006

### Taipei Office

11F, No. 115, Sec. 3, Min-Sheng East Rd.,  
Taipei, Taiwan  
TEL: 886-2-27190505  
FAX: 886-2-27197502

### Winbond Electronics (H.K.) Ltd.

Rm. 803, World Trade Square, Tower II,  
123 Hoi Bun Rd., Kwun Tong,  
Kowloon, Hong Kong  
TEL: 852-27513100  
FAX: 852-27552064

### Winbond Electronics North America Corp.

Winbond Memory Lab.  
Winbond Microelectronics Corp.  
Winbond Systems Lab.  
2727 N. First Street, San Jose,  
CA 95134, U.S.A.  
TEL: 408-9436666  
FAX: 408-5441798

Note: All data and specifications are subject to change without notice.